

Memory FeRAM

4M (512 K × 8) Bit SPI

MB85RS4MTY

■ DESCRIPTION

MB85RS4MTY is a FeRAM (Ferroelectric Random Access Memory) chip in a configuration of 524,288 words × 8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells. This product is targeted for high-temperature environment applications.

MB85RS4MTY adopts the Serial Peripheral Interface (SPI).

The MB85RS4MTY is able to retain data without using a back-up battery, as is needed for SRAM.

The memory cells used in the MB85RS4MTY can be used for 10^{13} read/write operations, which is a significant improvement over the number of read and write operations supported by Flash memory and E²PROM.

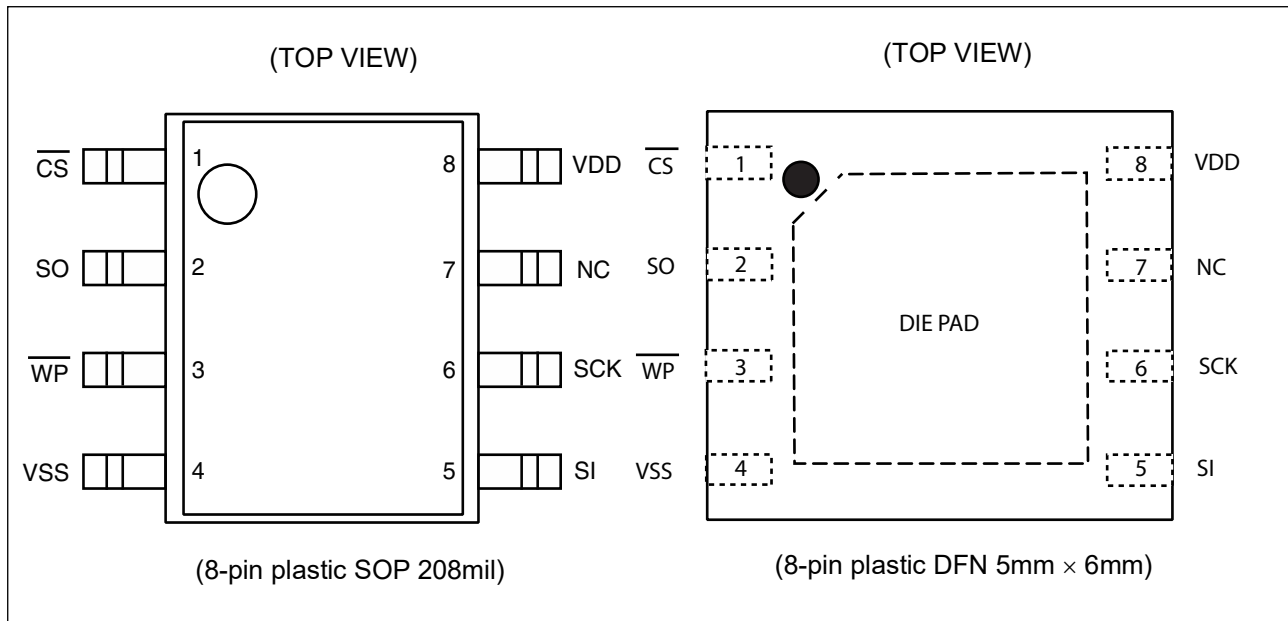
As MB85RS4MTY does not need any waiting time in writing process, the write cycle time of MB85RS4MTY is much shorter than that of Flash memories or E²PROM.

■ FEATURES

- Bit configuration : 524,288 words × 8 bits
- Special Sector Region : 256 words × 8 bits
In this region, data storage after (by) three times reflow based on JEDEC MSL-3 standard condition is guaranteed.
- Unique ID
- Serial Number : 64 bits
In this region, data storage after (by) three times reflow based on JEDEC MSL-3 standard condition is guaranteed.
- Serial Peripheral Interface : SPI (Serial Peripheral Interfaces)
Correspondent to SPI mode 0 (0, 0) and mode 3 (1, 1)
- Operating frequency : 50 MHz (Max)
- High endurance : 10^{13} times(+125°C), 10^{14} times(+85°C)
- Data retention : 70.4 years (+85 °C)
19.1 years (+105 °C)
5.9 years (+125 °C) or more
Under evaluation for more than 5.9 years(+125 °C)
- Operating power supply voltage : 1.8 V to 3.6 V
- Low power consumption : Operating power supply current 4 mA (Max@50 MHz)
Standby current 350 μA (Max)
Deep Power Down current 30 μA (Max)
Hibernate current 14 μA (Max)
- Operation ambient temperature range : - 40 °C to +125 °C
- Package : 8-pin plastic SOP 208mil
8-pin plastic DFN 5mm × 6mm
RoHS compliant

Fujitsu Semiconductor Memory Solutions Limited has changed its name to RAMXEED Limited. RAMXEED Limited will continue to offer and support existing products while maintaining Fujitsu's part number unchanged.

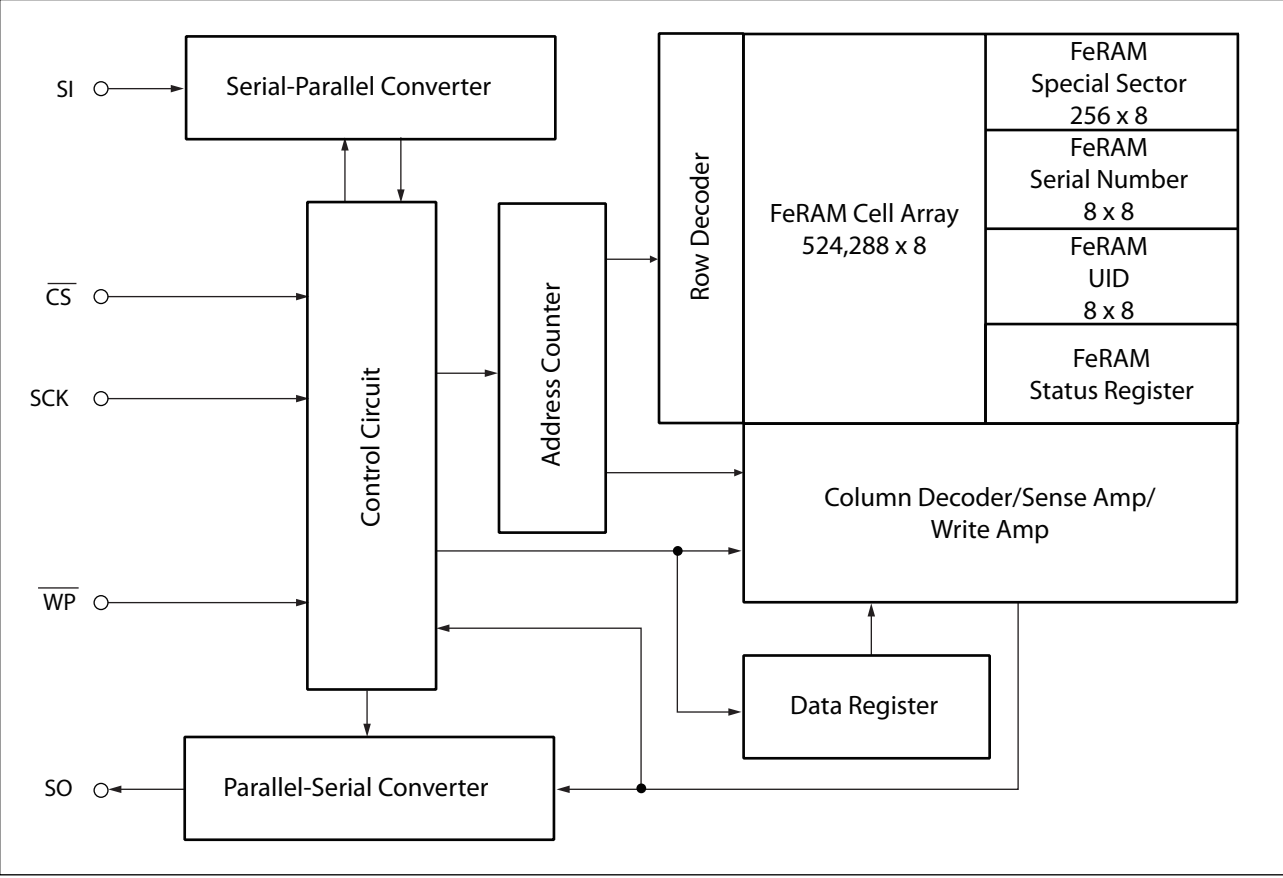
PIN ASSIGNMENT



PIN FUNCTIONAL DESCRIPTIONS

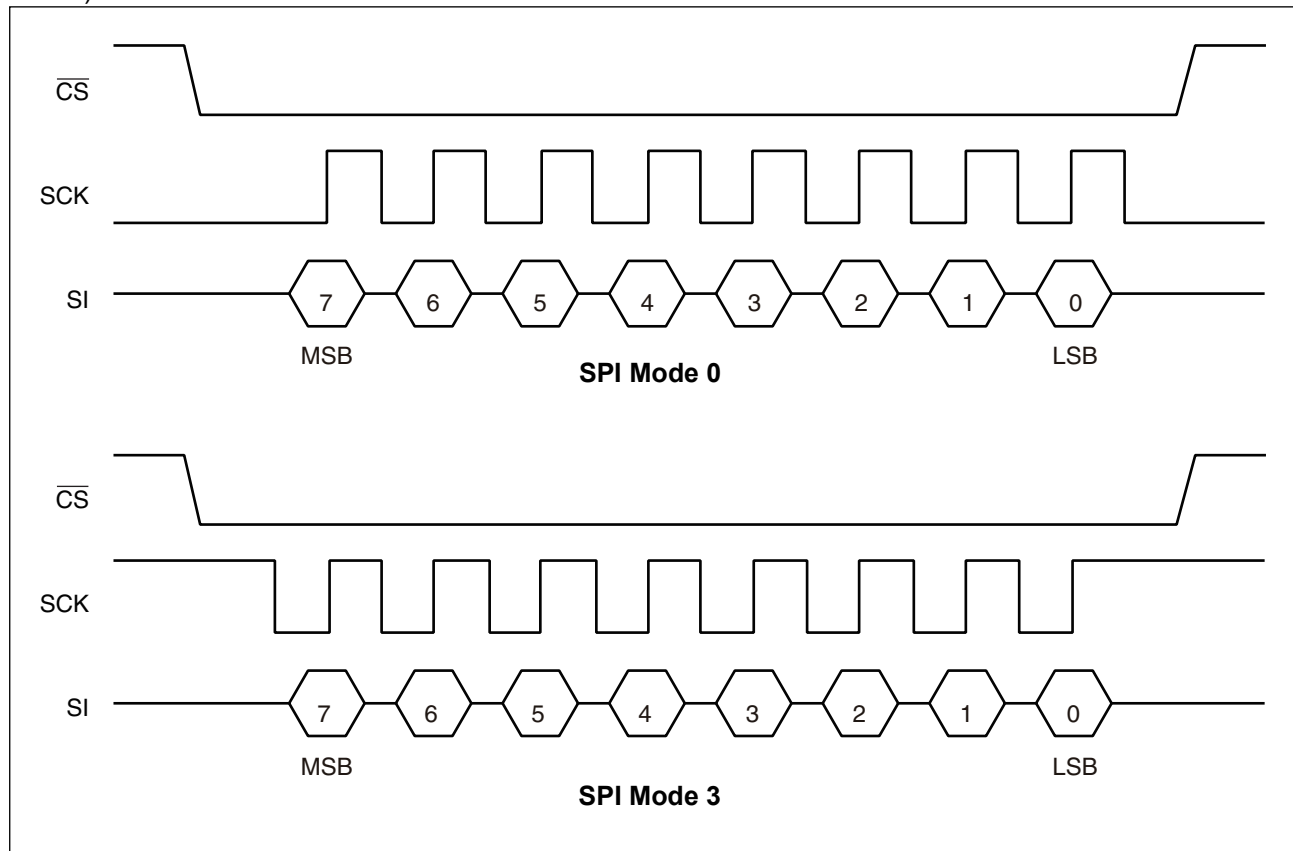
Pin No.	Pin Name	Functional description
1	\overline{CS}	Chip Select pin This is an input pin to make chips select. When \overline{CS} is "H" level, device is in deselect (standby) status and SO becomes High-Z. Inputs from other pins are ignored for this time. When \overline{CS} is "L" level, device is in select (active) status. \overline{CS} has to be "L" level before inputting op-code.
3	\overline{WP}	Write Protect pin This is a pin to control writing to a status register. The writing of status register (see "■ STATUS REGISTER") is protected in related with \overline{WP} and WPEN. See "■ WRITING PROTECT" for detail.
7	NC	NC pin This pin is not used. No connection or connecting VDD or VSS is allowed.
6	SCK	Serial Clock pin This is a clock input pin to input/output serial data. SI is loaded synchronously to a rising edge, SO is output synchronously to a falling edge.
5	SI	Serial Data Input pin This is an input pin of serial data. This inputs op-code, address, and writing data.
2	SO	Serial Data Output pin This is an output pin of serial data. Reading data of FeRAM memory cell array and status register data are output. This is High-Z during standby.
8	VDD	Supply Voltage pin
4	VSS	Ground pin
DIE PAD	—	It is allowed for the DIE PAD on the bottom of the DFN8 package to be floating (no connection to anything) or to be connected to VSS.

■ BLOCK DIAGRAM



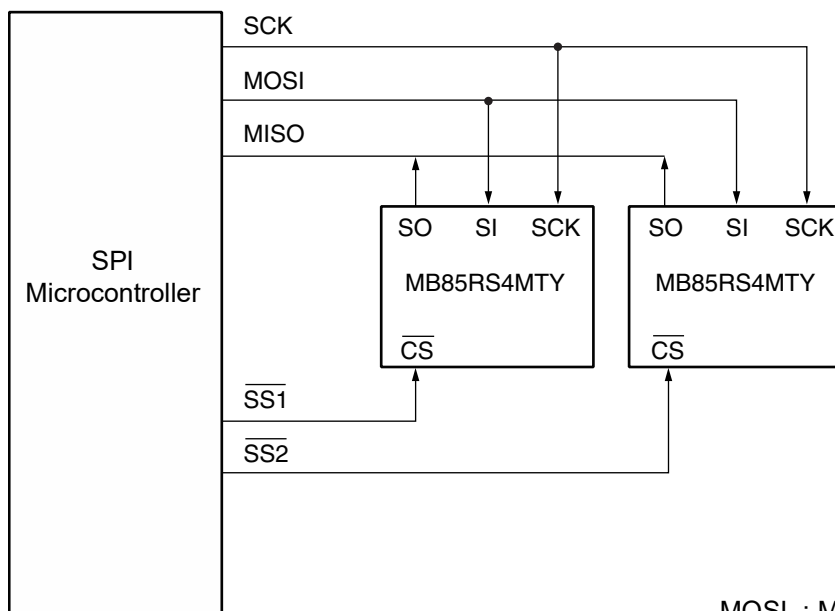
■ SPI MODE

MB85RS4MTY corresponds to the SPI mode 0 (CPOL = 0, CPHA = 0) , and SPI mode 3 (CPOL = 1, CPHA = 1) .



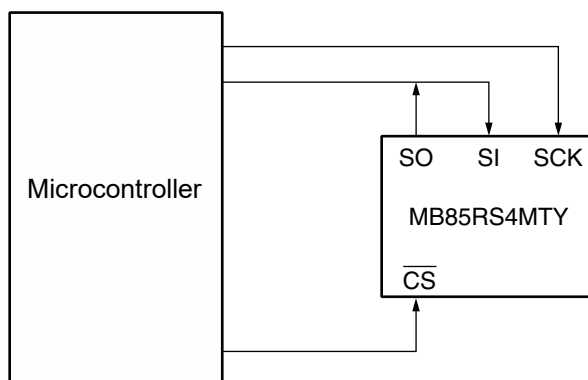
■ SERIAL PERIPHERAL INTERFACE (SPI)

MB85RS4MTY works as a slave of SPI. More than 2 devices can be connected by using microcontroller equipped with SPI port. By using a microcontroller not equipped with SPI port, SI and SO can be bus connected to use.



MOSI : Master Out Slave In
MISO : Master In Slave Out
SS : Slave Select

System Configuration with SPI Port



System Configuration without SPI Port

■ STATUS REGISTER

Bit No.	Bit Name	Function
7	WPEN	Status Register Write Protect This is a bit composed of nonvolatile memories (FeRAM). WPEN protects writing to a status register (refer to “■ WRITING PROTECT”) relating with \overline{WP} input. Writing with the WRSR command and reading with the RDSR command are possible.
6 to 4	—	Not Used Bits These are bits composed of nonvolatile memories, writing with the WRSR command is possible. These bits are not used but they are read with the RDSR command.
3	BP1	Block Protect This is a bit composed of nonvolatile memory. This defines size of write protect block for the WRITE command (refer to “■ BLOCK PROTECT”). Writing with the WRSR command and reading with the RDSR command are possible.
2	BP0	
1	WEL	Write Enable Latch This indicates FeRAM Array and status register are writable. The WREN command is for setting, and the WRDI command is for resetting. With the RDSR command, reading is possible but writing is not possible with the WRSR command. WEL is reset after the following operations. After power ON. After WRDI command recognition. After return from DPD mode. After return from Hibernate mode. After release from reset. Achieving continuous writing mode, WEL is not reset after following operations making it possible to execute writing commands continuously. After WRSR command recognition. After WRITE command recognition. After WRSN command recognition. After SSWR command recognition.
0	0	This is a bit fixed to “0”.

■ OP-CODE

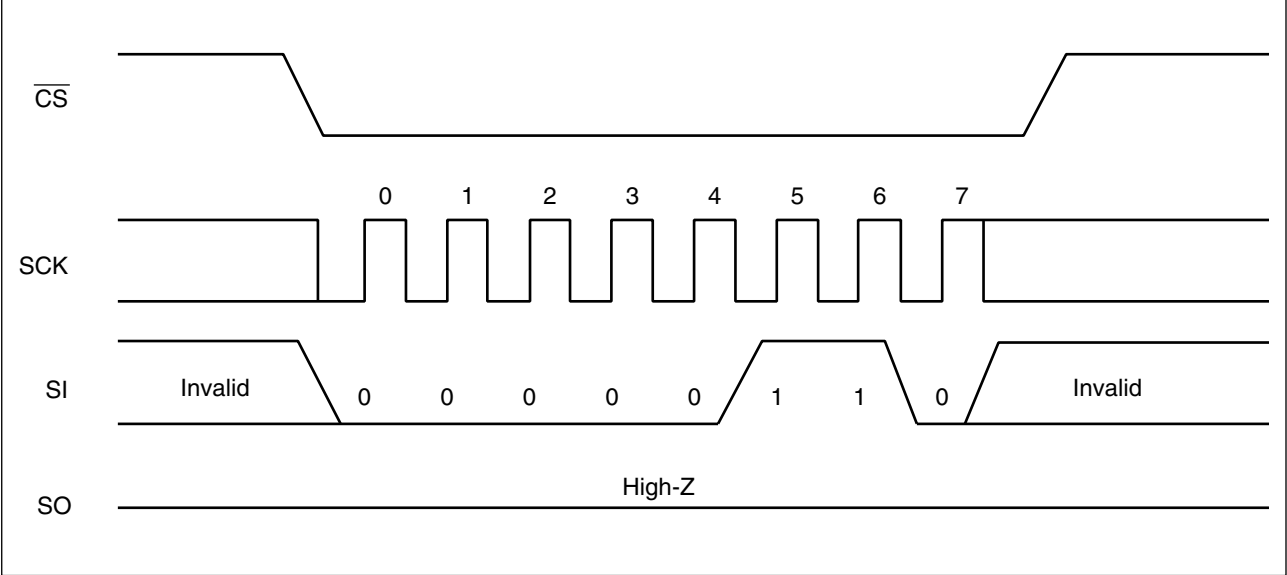
MB85RS4MTY accepts 16 kinds of command specified in op-code. Op-code is a code composed of 8 bits shown in the table below. Do not input invalid codes other than those codes. If \overline{CS} is risen while inputting op-code, the command are not performed.

Name	Description	Op-code
WREN	Set Write Enable Latch	0000 0110 _B
WRDI	Reset Write Enable Latch	0000 0100 _B
RDSR	Read Status Register	0000 0101 _B
WRSR	Write Status Register	0000 0001 _B
READ	Read Memory Code	0000 0011 _B
WRITE	Write Memory Code	0000 0010 _B
FSTRD	Fast Read Memory Code	0000 1011 _B
DPD	Deep Power Down Mode	1011 1010 _B
HIBERNATE	Hibernate Mode	1011 1001 _B
RDID	Read Device ID	1001 1111 _B
RUID	Read Unique ID	0100 1100 _B
WRSN	Write Serial Number	1100 0010 _B
RDSN	Read Serial Number	1100 0011 _B
SSWR	Write Special Sector	0100 0010 _B
SSRD	Read Special Sector	0100 1011 _B
FSSRD	Fast Read Special Sector	0100 1001 _B
RFU	Reserved	1100 1110 _B
		1100 1111 _B
		1100 1100 _B

■ COMMAND

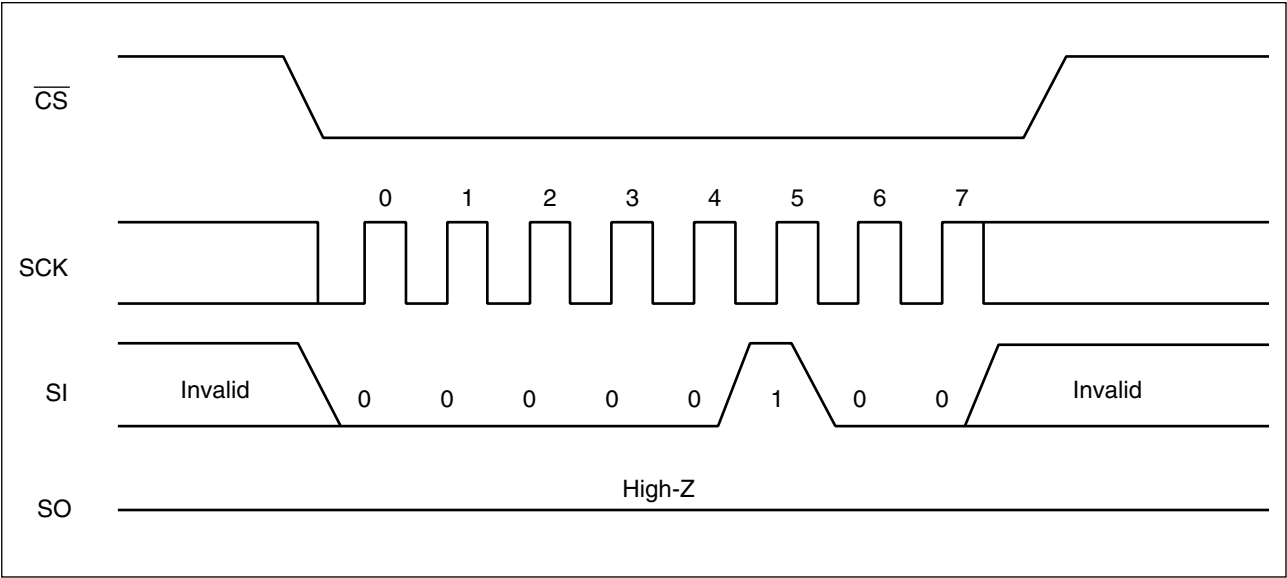
• WREN

The WREN command sets WEL (Write Enable Latch) bit to 1. WEL has to be set with the WREN command before writing operation (WRSR command, WRITE command, WRSN command and SSWR command) .



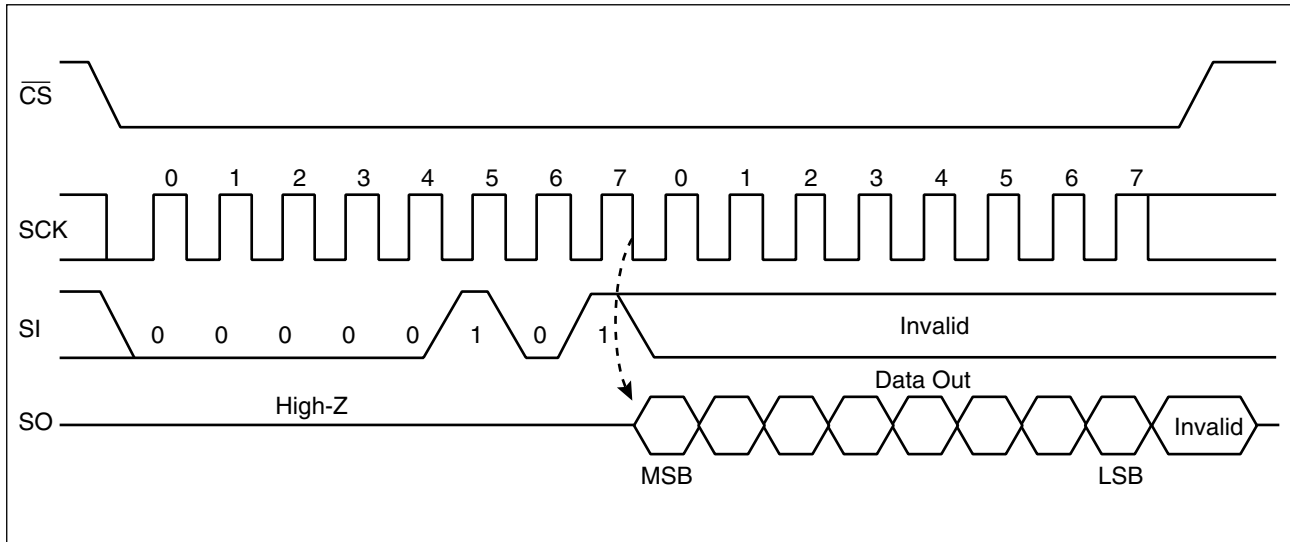
• WRDI

The WRDI command resets WEL (Write Enable Latch) bit to 0. Writing operation (WRSR command, WRITE command, WRSN command and SSWR command) are not performed when WEL is reset.



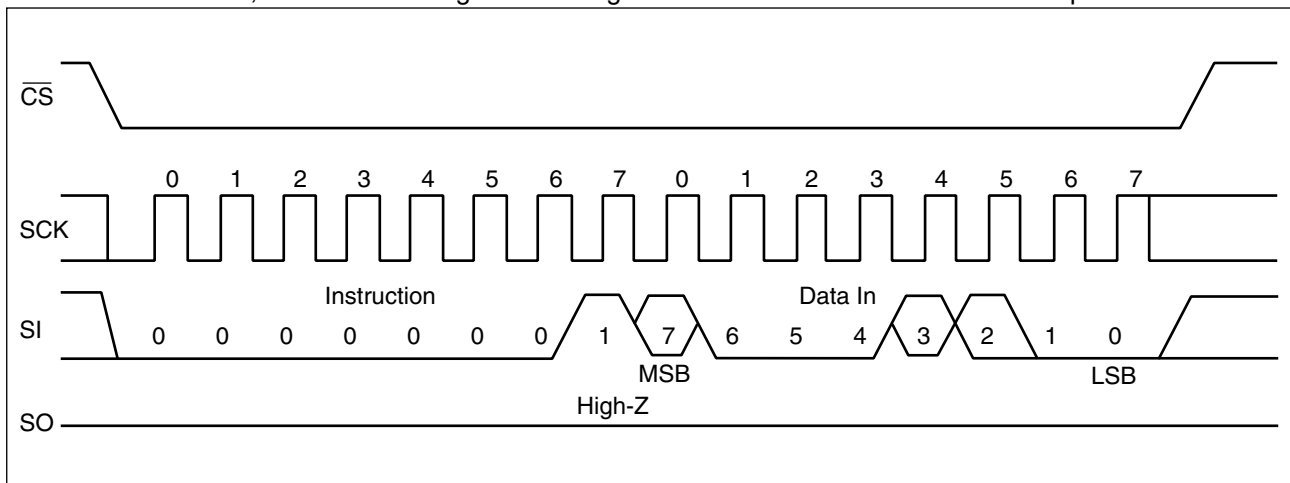
• RDSR

The RDSR command reads status register data. After op-code of RDSR is input to SI, 8-cycle clock is input to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK. In the RDSR command, repeated reading of status register is enabled by sending SCK continuously before rising of \overline{CS} .



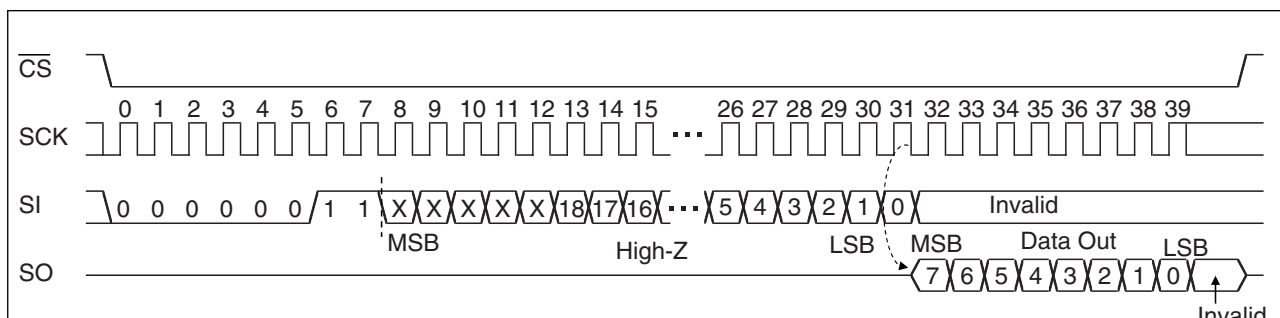
• WRSR

The WRSR command writes data to the nonvolatile memory bit of status register. After performing WRSR op-code to a SI pin, 8 bits writing data is input. WEL (Write Enable Latch) is not able to be written with WRSR command. A SI value correspondent to bit 1 is ignored. Bit 0 of the status register is fixed to "0" and cannot be written. The SI value corresponding to bit 0 is ignored. \overline{WP} signal level shall be fixed before performing WRSR command, and do not change the \overline{WP} signal level until the end of command sequence.



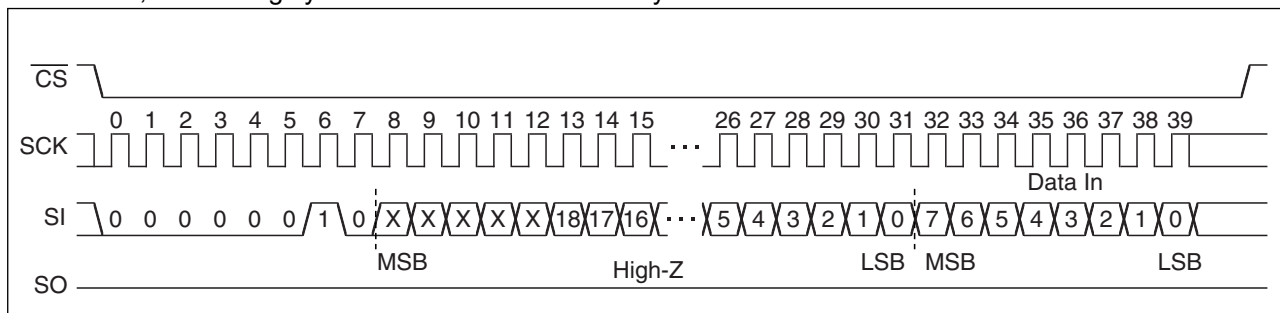
• READ

The READ command reads FeRAM memory cell array data. Arbitrary 24 bits address and op-code of READ are input to SI. The 5-bit upper address bit is invalid. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When \overline{CS} is risen, the READ command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before \overline{CS} rising. When it reaches the most significant address, it rolls over to the starting address, and reading cycle keeps on infinitely.



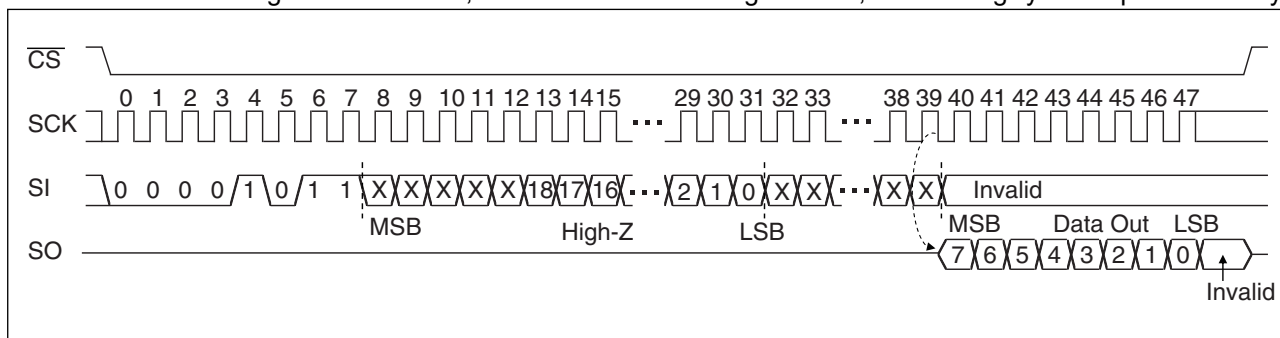
• WRITE

The WRITE command writes data to FeRAM memory cell array. WRITE op-code, arbitrary 24 bits of address and 8 bits of writing data are input to SI. The 5-bit upper address bit is invalid. When 8 bits of writing data is input, data is written to FeRAM memory cell array. Risen \overline{CS} will terminate the WRITE command, but if you continue sending the writing data for 8 bits each before \overline{CS} rising, it is possible to continue writing with automatic address increment. When it reaches the most significant address, it rolls over to the starting address, and writing cycle can be continued infinitely.



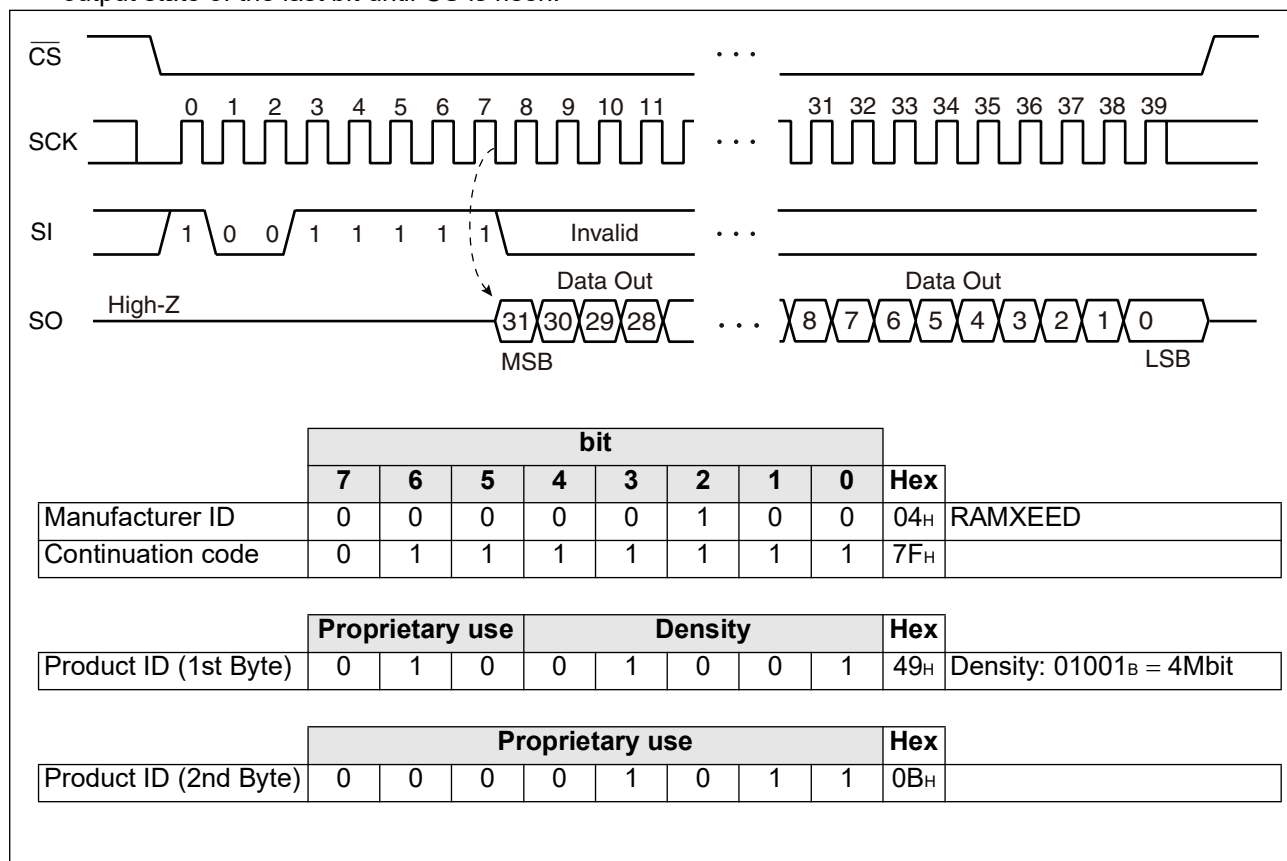
• FSTRD

The FSTRD command reads FeRAM memory cell array data. Arbitrary 24 bits address and op-code of FSTRD are input to SI followed by 8 bits dummy. The 5-bit upper address bit is invalid. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When \overline{CS} is risen, the FSTRD command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before \overline{CS} rising. When it reaches the most significant address, it rolls over to the starting address, and reading cycle keeps on infinitely.



• RDID

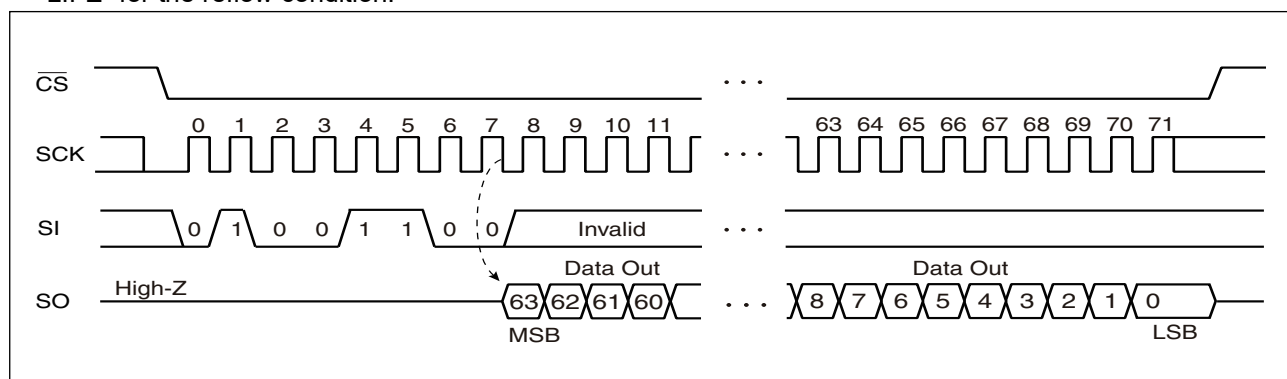
The RDID command reads fixed Device ID. After performing RDID op-code to SI, 32-cycle clock is input to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK. The output is in order of Manufacturer ID (8bit)/Continuation code (8bit)/Product ID (1st Byte)/Product ID (2nd Byte). In the RDID command, 32-bit Device ID is output by continuously sending SCK clock, and SO holds the output state of the last bit until \overline{CS} is risen.



• RUID

The RUID command reads an unique ID which is defined in 64bits for each device. After performing RUID op-code to SI, 64-cycle clock is input to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK.

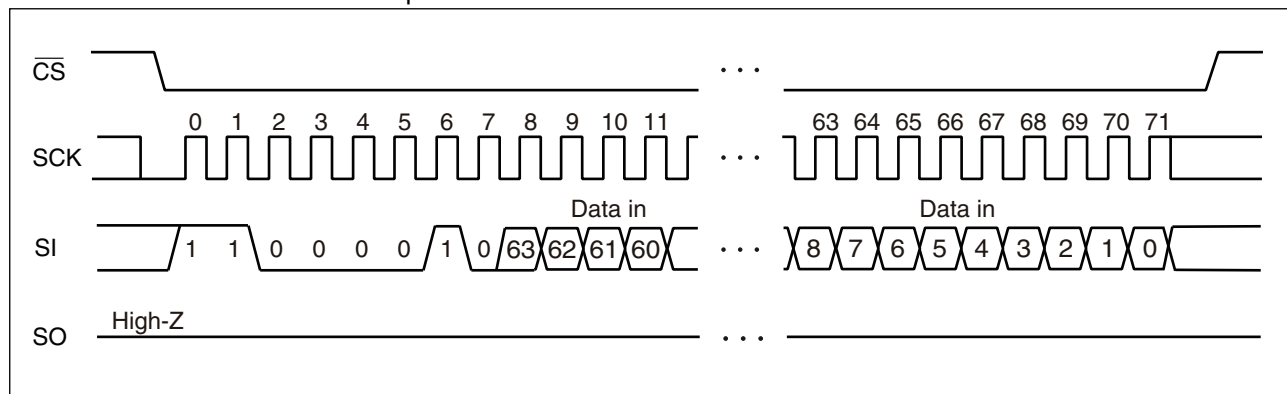
The unique ID is stable between before and after reflow. Refer “■ REFLOW CONDITIONS AND FLOOR LIFE” for the reflow condition.



•WRSN

The WRSN command writes data to serial number region which is allowed to write only one time. After performing WRSN op-code to SI, 64bits of writing data is input. Once wrote, the serial number region is protected, disabling to overwrite even when issuing WRSN command.

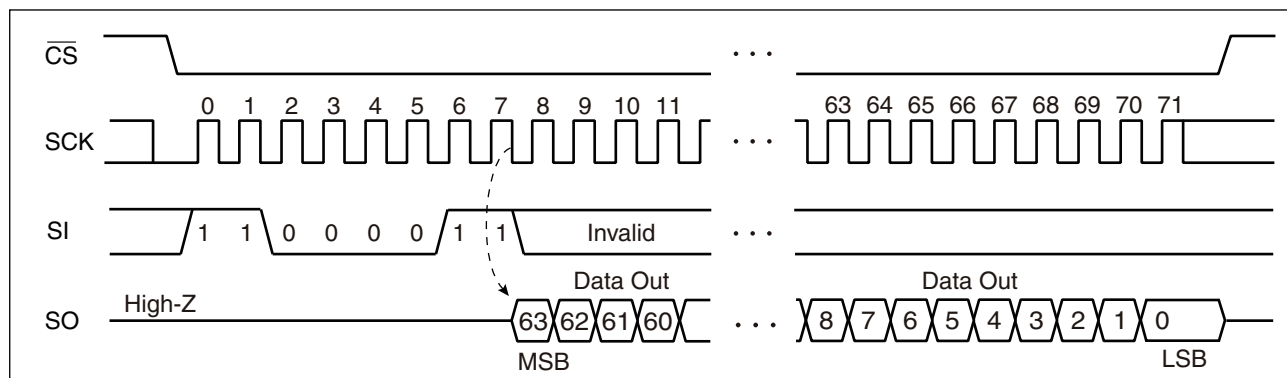
\overline{WP} signal level shall be fixed before performing WRSN command, and do not change the \overline{WP} signal level until the end of command sequence.



•RDSN

The RDSN command reads 64 bits of serial number which is written using WRSN command. After performing RDSN op-code to SI, 64-cycle clock to SCK. The SI value is invalid for this time. SO is output synchronously to a falling edge of SCK. When reading serial number from devices which no WRSN command is executed, "0" for all bits are output.

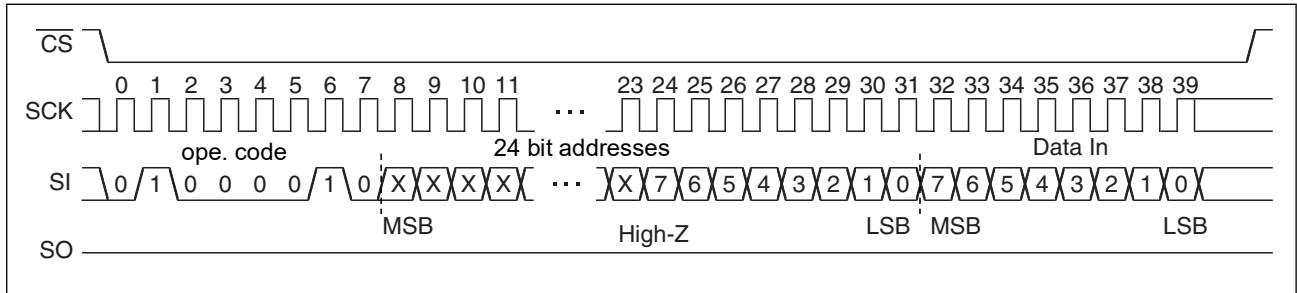
The serial number is stable between before and after reflow. Refer "■ REFLOW CONDITIONS AND FLOOR LIFE" for the reflow condition.



• SSWR

The SSWR command writes data to special sector (a special region of 256 Byte in FeRAM). SSWR op-code, arbitrary 24 bits address and 8-bit writing data are input to SI. The 16-bit upper address is invalid. When input of 8-bit writing data is completed, it starts writing data to special sector. Risen \overline{CS} will terminate the SSWR command, but if you continue the writing data for each before \overline{CS} rising, it is possible to continue writing with automatic address increment. When it reaches the most significant address, roll over is not happen, the data hereafter is ignored.

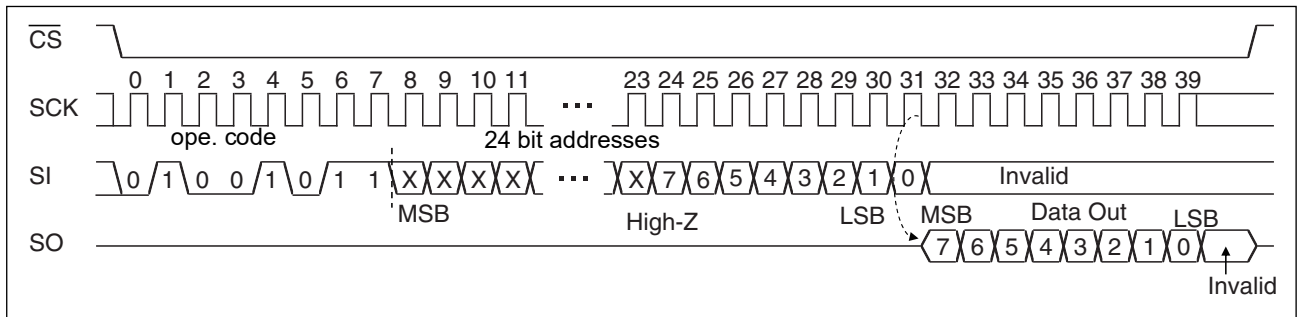
The data in special sector is stable between before and after reflow. Refer “■ REFLOW CONDITIONS AND FLOOR LIFE” for the reflow condition.



• SSRD

The SSRD command reads data from special sector (a special region of 256 Byte in FeRAM). SSWR op-code and arbitrary 24 bits address are input to SI. The 16-bit upper address is invalid. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When \overline{CS} is risen, the SSRD command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before \overline{CS} rising. When it reaches the most significant address, roll over is not happen.

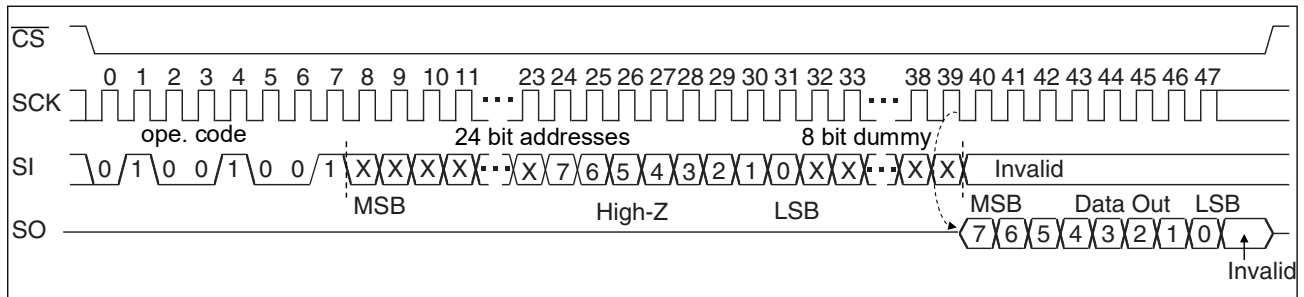
The data in special sector is stable between before and after reflow. Refer “■ REFLOW CONDITIONS AND FLOOR LIFE” for the reflow condition.



• FSSRD

The SSRD command reads data from special sector (a special region of 256 Byte in FeRAM). SSWR op-code and arbitrary 24 bits address are input to SI followed by 8 bits dummy. The 16-bit upper address is invalid. Then, 8-cycle clock is input to SCK. SO is output synchronously to the falling edge of SCK. While reading, the SI value is invalid. When \overline{CS} is risen, the SSRD command is completed, but keeps on reading with automatic address increment which is enabled by continuously sending clocks to SCK in unit of 8 cycles before \overline{CS} rising. When it reaches the most significant address, roll over is not happen.

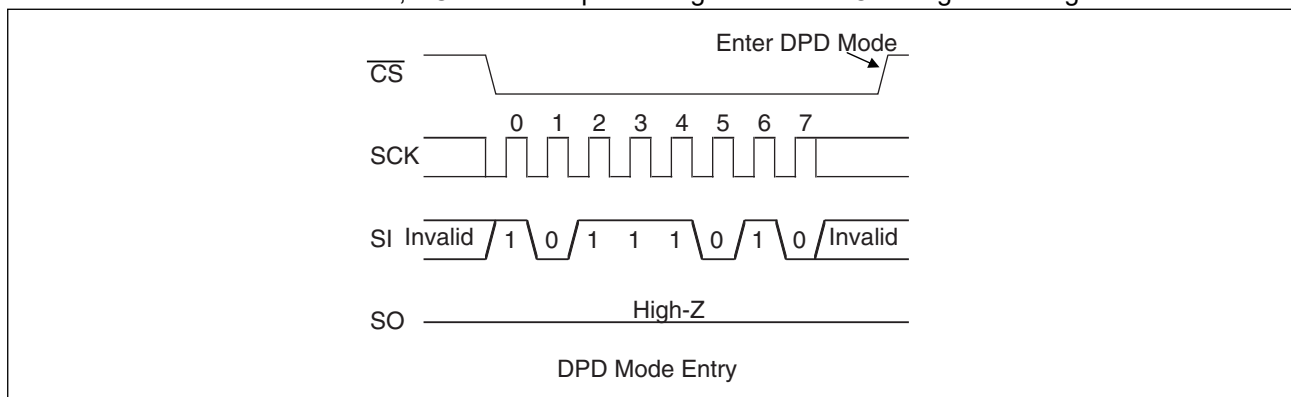
The data in special sector is stable between before and after reflow. Refer “■ REFLOW CONDITIONS AND FLOOR LIFE” for the reflow condition.



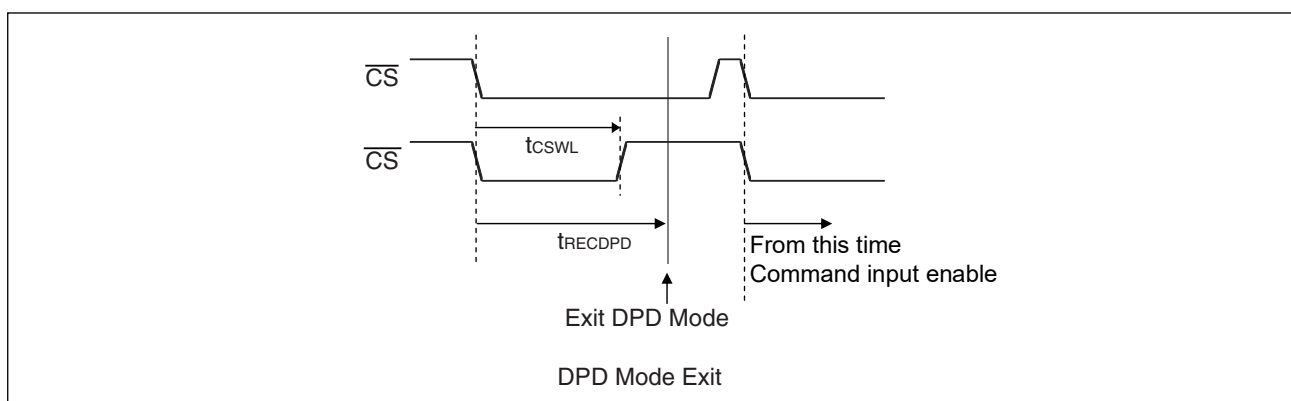
• DPD(Deep Power Down)

The DPD command shifts the LSI to a low power mode called “DPD mode”. The transition to the DPD mode is carried out at the rising edge of \overline{CS} after operation code in the DPD command. However, when at least one SCK clock is inputted before the rising edge of \overline{CS} after operation code in the DPD command, this DPD command is canceled.

After the DPD mode transition, SCK and SI inputs are ignored and SO changes to a High-Z state.



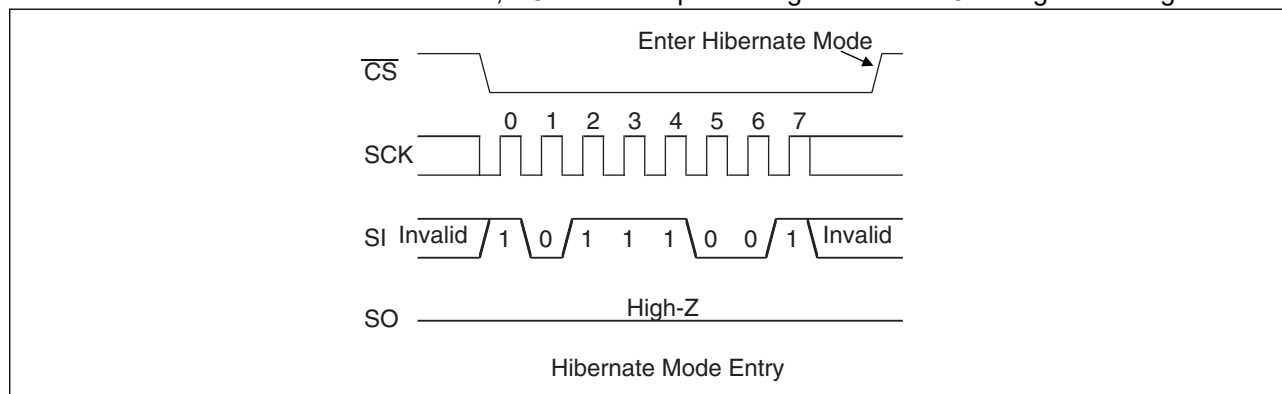
Returning to an normal operation from the DPD mode is carried out after t_{RECDPD} (Max 10 μ s) time from the falling edge of \overline{CS} (see the figure below). It is possible to return \overline{CS} to H level before t_{RECDPD} time. However, it is prohibited to bring down \overline{CS} to L level again during t_{RECDPD} period.



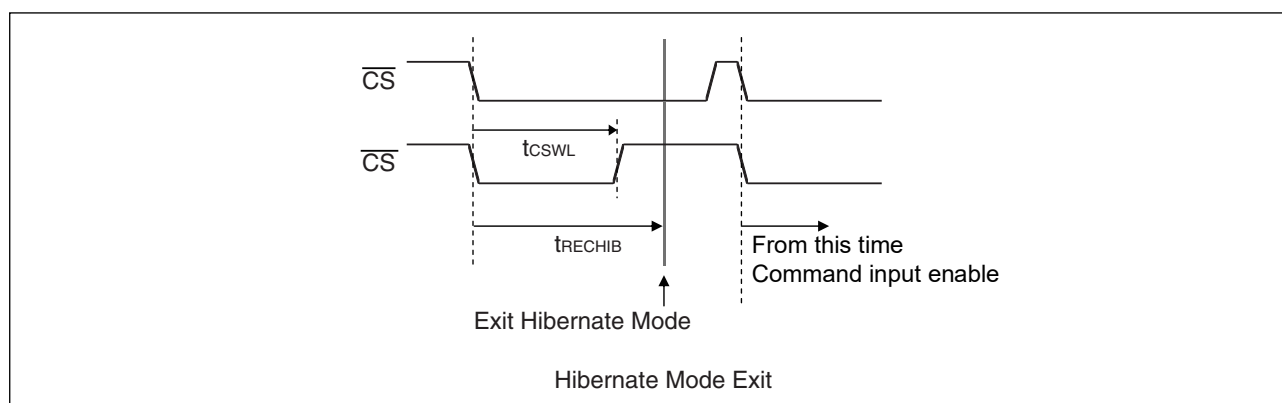
• HIBERNATE

The HIBERNATE command shifts the LSI to a low power mode called "HIBERNATE mode". The transition to the HIBERNATE mode is carried out at the rising edge of \overline{CS} after operation code in the HIBERNATE command. However, when at least one SCK clock is inputted before the rising edge of \overline{CS} after operation code in the HIBERNATE command, this HIBERNATE command is canceled.

After the HIBERNATE mode transition, SCK and SI inputs are ignored and SO changes to a High-Z state.



Returning to a normal operation from the HIBERNATE mode is carried out after t_{RECHIB} (Max 450 μ s) time from the falling edge of \overline{CS} (see the figure below). It is possible to return \overline{CS} to H level before t_{RECHIB} time. However, it is prohibited to bring down \overline{CS} to L level again during t_{RECHIB} period.



■ BLOCK PROTECT

Writing protect block for WRITE command is configured by the value of BP0 and BP1 in the status register.

BP1	BP0	Protected Block
0	0	None
0	1	60000 _H to 7FFFF _H (upper 1/4)
1	0	40000 _H to 7FFFF _H (upper 1/2)
1	1	00000 _H to 7FFFF _H (all)

■ WRITING PROTECT

Writing operation of the WRITE command and the WRSR command are protected with the value of WEL, WPEN, WP as shown in the table.

WEL	WPEN	WP	Protected Blocks	Unprotected Blocks	Status Register
0	X	X	Protected	Protected	Protected
1	0	X	Protected	Unprotected	Unprotected
1	1	0	Protected	Unprotected	Protected
1	1	1	Protected	Unprotected	Unprotected

■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Unit
		Min	Max	
Power supply voltage*	V_{DD}	- 0.5	+ 4.0	V
Input voltage*	V_{IN}	- 0.5	$V_{DD} + 0.5 (\leq 4.0)$	V
Output voltage*	V_{OUT}	- 0.5	$V_{DD} + 0.5 (\leq 4.0)$	V
Operation ambient temperature	T_A	- 40	+ 125	°C
Storage temperature	T_{stg}	- 55	+ 150	°C

*: These parameters are based on the condition that V_{SS} is 0 V.

WARNING: Semiconductor devices may be permanently damaged by application of stress (including, without limitation, voltage, current or temperature) in excess of absolute maximum ratings.
Do not exceed any of these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Power supply voltage*1	V_{DD}	1.8	3.3	3.6	V
Operation ambient temperature*2	T_A	- 40	—	+ 125	°C

*1: These parameters are based on the condition that V_{SS} is 0 V.

*2: Ambient temperature when only this device is working. Please consider it to be the almost same as the package surface temperature.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated under these conditions.

Any use of semiconductor devices will be under their recommended operating condition.
Operation under any conditions other than these conditions may adversely affect reliability of device and could result in device failure.

No warranty is made with respect to any use, operating conditions or combinations not represented on this data sheet. If you are considering application under any conditions other than listed herein, please contact sales representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

Parameter	Symbol	Condition		Value			Unit
				Min	Typ	Max	
Input leakage current*1	$ I_{Li} $	$\overline{CS} = V_{DD}$	25 °C	—	—	1	μA
			125 °C	—	—	2	
		$\overline{WP}, \overline{SCK}, \overline{CS}$ $SI = 0 V \text{ to } V_{DD}$	25 °C	—	—	1	
			125 °C	—	—	2	
Output leakage current*2	$ I_{Lo} $	$SO = 0 V \text{ to } V_{DD}$	25 °C	—	—	1	μA
			125 °C	—	—	2	
Operating power supply current*3	I_{DD}	$SCK = 50MHz$		—	3.5	4	mA
Standby current	I_{SB}	$SCK = SI = \overline{CS} = \overline{WP} = V_{DD}$		—	11.0	350	μA
Hibernate current	I_{ZZHIB}	$\overline{CS} = V_{DD}$ All inputs V_{SS} or V_{DD}		—	0.1	14	μA
DPD current	I_{ZZDPD}	$\overline{CS} = V_{DD}$ All inputs V_{SS} or V_{DD}		—	5.0	30	μA
Input high voltage	V_{IH}	$V_{DD} = 1.8 V \text{ to } 3.6 V$		$V_{DD} \times 0.7$	—	$V_{DD} + 0.5$	V
Input low voltage	V_{IL}	$V_{DD} = 1.8 V \text{ to } 3.6 V$		- 0.5	—	$V_{DD} \times 0.3$	V
Output high voltage	V_{OH}	$I_{OH} = - 2 mA$		$V_{DD} - 0.5$	—	—	V
Output low voltage	V_{OL}	$I_{OL} = 2 mA$		—	—	0.4	V

*1 : Applicable pin : \overline{CS} , \overline{WP} , SCK , SI

*2 : Applicable pin : SO

*3 : Input voltage magnitude : $V_{DD} - 0.2 V$ or V_{SS}

2. AC Characteristics

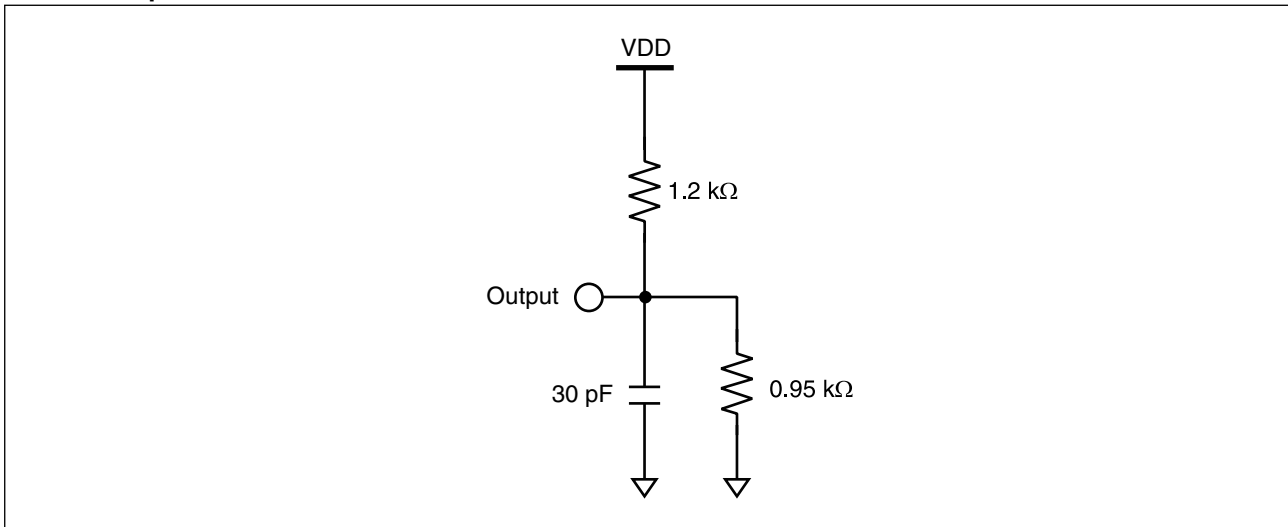
Parameter	Symbol	Value		Unit	Condition V _{DD}
		Min	Max		
SCK clock frequency	f _{CK}	—	50	MHz	all commands except for READ/SSRD
		—	40		READ command
		—	10		SSRD command
Clock high time	t _{CH}	9	—	ns	
Clock low time	t _{CL}	9	—	ns	
Chip select set up time	t _{CSU}	5	—	ns	
Chip select hold time	t _{CSH}	5	—	ns	
Output disable time	t _{OD}	—	10	ns	
Output data valid time	t _{ODV}	—	9	ns	*1
Output hold time	t _{OH}	0	—	ns	
Deselect time	t _D	40	—	ns	
Data in rising time	t _R	—	50	ns	
Data falling time	t _F	—	50	ns	
Data set up time	t _{SU}	5	—	ns	
Data hold time	t _H	5	—	ns	
DPD/Hibernate recovery pulse width	t _{CSWL}	100	—	ns	
DPD recovery time	t _{RECDPD}	—	10	μs	
Hibernate recovery time	t _{RECHIB}	—	450	μs	

*1: In SSRD command, 60ns(max.)

AC Test Condition

Power supply voltage : 1.8 V to 3.6 V Operation
 Operation ambient temperature : - 40 °C to + 125 °C
 Input voltage magnitude : $V_{DD} \times 0.8 \leq V_{IH} \leq V_{DD}$
 $0 \leq V_{IL} \leq V_{DD} \times 0.2$
 Input rising time : 5 ns
 Input falling time : 5 ns
 Input judge level : $V_{DD}/2$
 Output judge level : $V_{DD}/2$

AC Load Equivalent Circuit

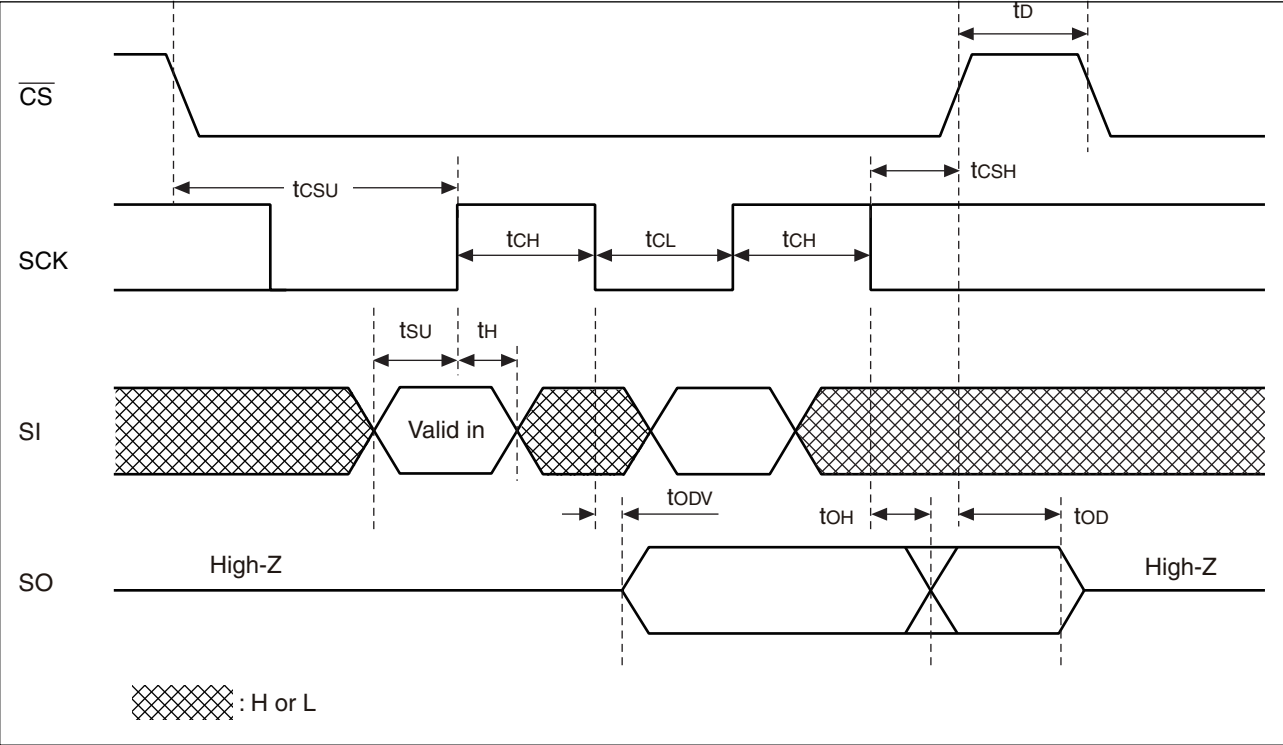


3. Pin Capacitance

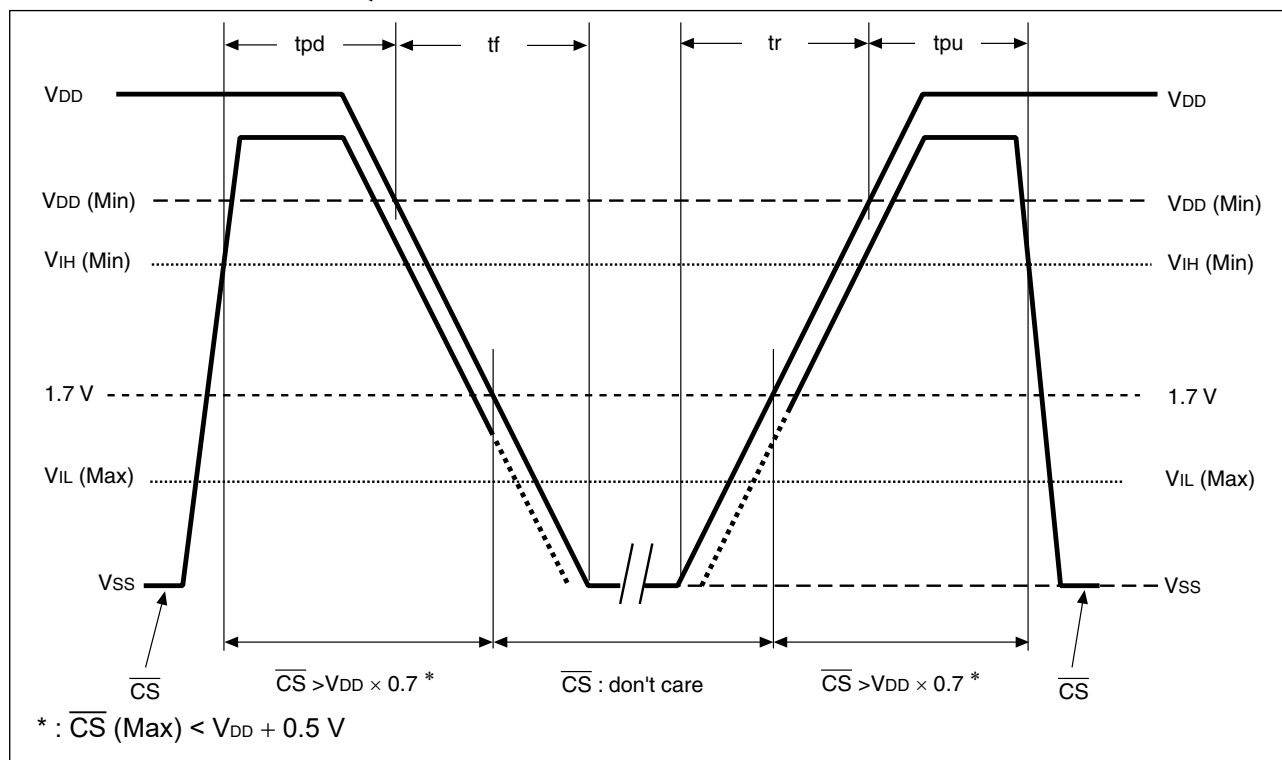
Parameter	Symbol	Condition	Value		Unit
			Min	Max	
Output capacitance	C_O	$V_{DD} = 3.3 \text{ V}$, $V_{IN} = V_{OUT} = 0 \text{ V to } V_{DD}$, $f = 1 \text{ MHz}$, $T_A = +25 \text{ }^\circ\text{C}$	—	8	pF
Input capacitance	C_I		—	6	pF

■ TIMING DIAGRAM

• Serial Data Timing



■ POWER ON/OFF SEQUENCE



In case relative short V_{DD} pulse whose peak level is beyond 1.7 is applied, please set V_{DD} falling time, t_f , longer than 0.4ms/V. (When V_{DD} rises beyond 1.7V, and falls just after, if this term is very short the device may lose its function.).

Parameter	Symbol	Value		Unit	Condition V_{DD}
		Min	Max		
\overline{CS} level hold time at power OFF	tpd	400	—	ns	1.8V to 2.7V
		0	—		2.7V to 3.6V
\overline{CS} level hold time at power ON	tpu	450	—	μs	—
Power supply rising time	tr	0.05	—	ms/V	—
Power supply falling time	tf	0.1	—	ms/V	—

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

■ FeRAM CHARACTERISTICS

Parameter	Value		Unit	Remarks
	Min	Max		
Read/Write Endurance*1	10 ¹³	—	Times	Operation Ambient Temperature T _A = + 125 °C
	10 ¹⁴	—		Operation Ambient Temperature T _A = + 85 °C
Data Retention*2	5.9 or more*3	—	Years	Operation Ambient Temperature T _A = + 125 °C
	19.1	—		Operation Ambient Temperature T _A = + 105 °C
	70.4	—		Operation Ambient Temperature T _A = + 85 °C

*1: For details on the Read/Write endurance value, please refer to “■Read/Write endurance about FeRAM”.

*2: Minimum values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

*3: Under evaluation for more than 5.9 years(+125 °C).

■ NOTE ON USE

We recommend programming of the device after reflow except for special sector region and serial number region. Data written before reflow cannot be guaranteed.

■ Read/Write endurance about FeRAM

The value for Read/Write endurance apply to the total number of read and write operations per row in FeRAM. This is because FeRAM needs writing operation after each reading operations. Each row in the memory array has 32 internal outputs, and 8 outputs are selected by A0 and A1. In continuous Read/Write operations, after selecting a certain address and automatically incrementing until A0 and A1 change from (0,0) to (1,1), the Read/Write count endurance count is totaled as one operation. Subsequently, when incrementing automatically and switching to the next row, each row is counted as a new Read/Write operation. If /CS is raised and then the same row is selected again, it is counted as the second operation for that row.

As an actual usage example, if you loop through and access only a memory area (64 bytes or 256 bytes) specified by a specific address in the entire memory area, the number of years it will take to reach 10¹⁴ times is as below.

As shown here, with a write endurance of 10¹⁴ times, even in extreme cases there is enough time before the upper limit is reached, and under normal conditions of use it can be used without worrying about the number of writes/reads.

Operating frequency	Years reached when looping continuously through 64 byte area	Years reached when looping continuously through 256 byte area
50MHz	34.1	131
40MHz	42.6	164
20MHz	85.1	328
10MHz	170.0	657

■ ESD AND LATCH-UP

(8-pin plastic SOP 208mi)

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant	MB85RS4MTYPF-G-BCE1 MB85RS4MTYPF-G-BCERE1	$\geq 2000 \text{ V} $
ESD CDM (Charged Device Model) JESD22-C101		$\geq 1500 \text{ V} $
Latch-Up (I-test) JESD78 compliant		$\geq 125\text{mA} $
Latch-Up (V_{supply} overvoltage test) JESD78 compliant		$\geq 5.4\text{V}$

(8-pin plastic DFN 5mm × 6mm)

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant	MB85RS4MTYPN-G-AWEWE1	$\geq 2000 \text{ V} $
ESD CDM (Charged Device Model) JESD22-C101		$\geq 750 \text{ V} $
Latch-Up (I-test) JESD78 compliant		$\geq 125\text{mA} $
Latch-Up (V_{supply} overvoltage test) JESD78 compliant		$\geq 5.4\text{V}$

■ REFLOW CONDITIONS AND FLOOR LIFE

[JEDEC MSL] : Moisture Sensitivity Level 3 (IPC/JEDEC J-STD-020E)

■ Current status on Contained Restricted Substances

This product complies with the regulations of REACH Regulations, EU RoHS Directive and China RoHS.

■ ORDERING INFORMATION

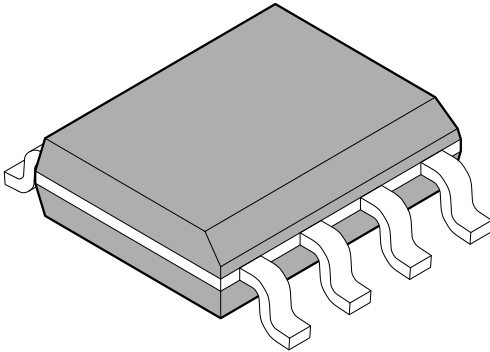
Part number	Package	Shipping form	Minimum shipping quantity
MB85RS4MTYPF-G-BCE1	8-pin plastic SOP (208mil)	Tube	— *
MB85RS4MTYPF-G-BCERE1	8-pin plastic SOP (208mil)	Embossed Carrier tape	500
MB85RS4MTYPN-G-AWEWE1	8-pin plastic DFN	Embossed Carrier tape	1500

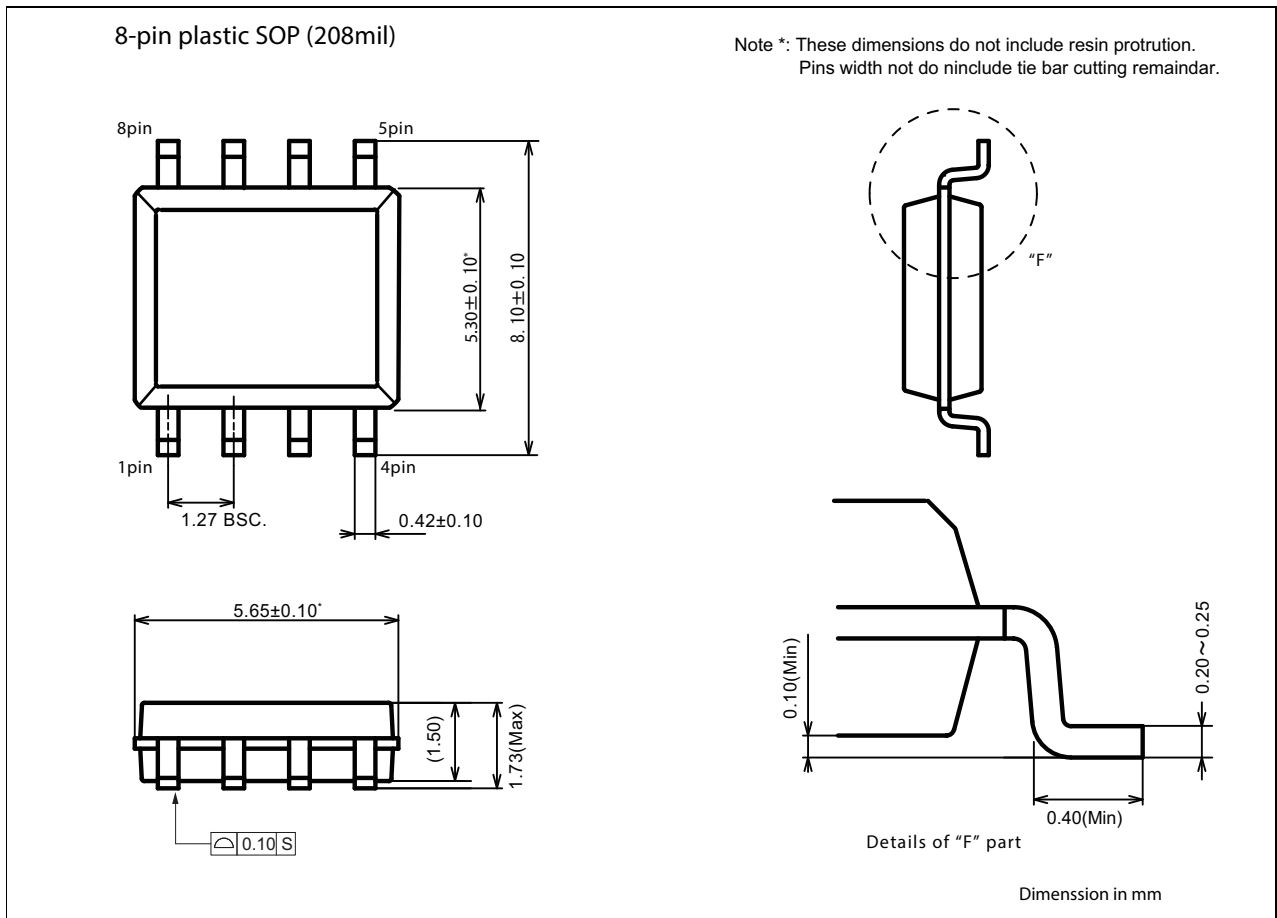
* : Please contact our sales office about minimum shipping quantity.

MB85RS4MTY

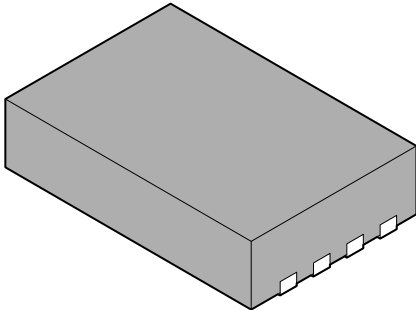
■ PACKAGE DIMENSION

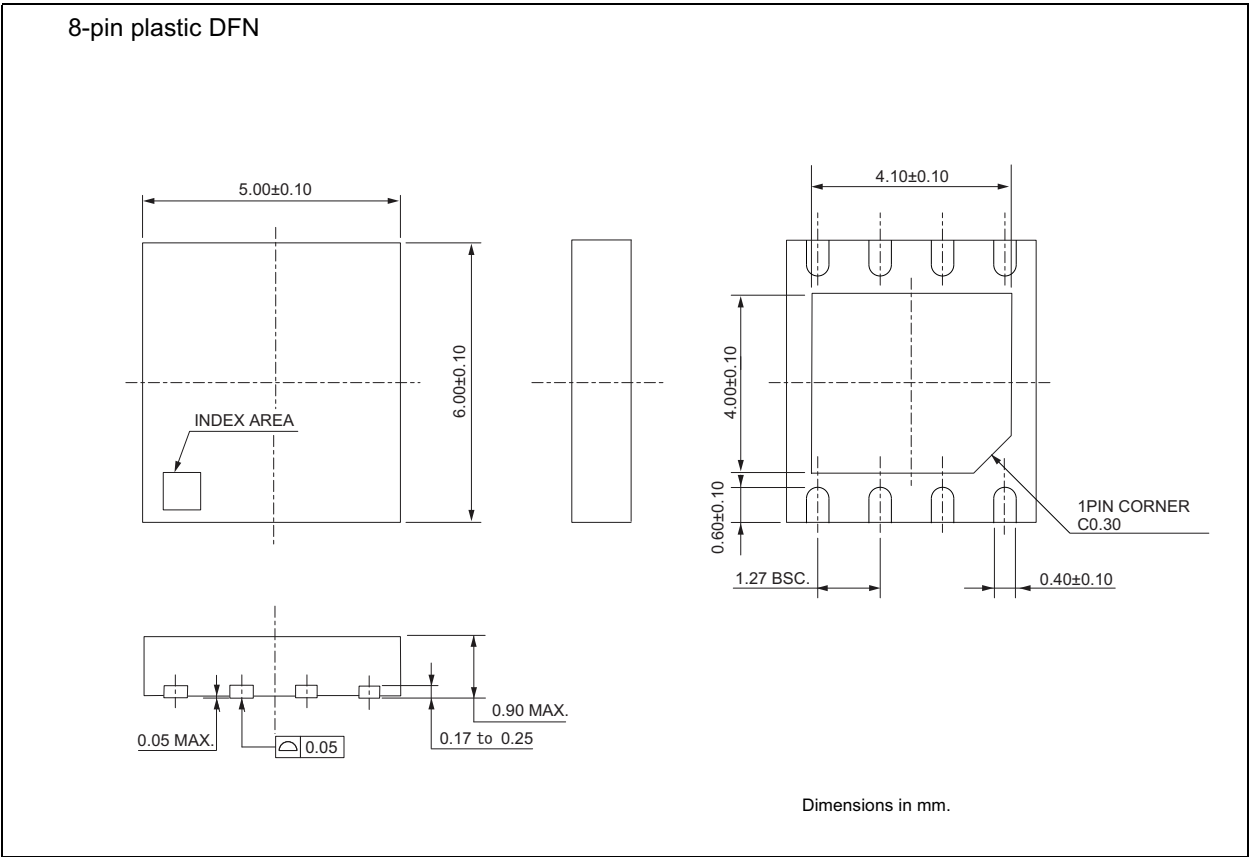
(1) MB85RS4MTYPF-G-BCE1/MB85RS4MTYPF-G-BCERE1

 <p>8-pin plastic SOP (208mil)</p>	Lead pitch	1.27 mm
	Package width × package length	5.30 mm × 5.65 mm
	Lead shape	Gullwing
	Sealing method	Plastic mold
	Mounting height	1.73 mm MAX



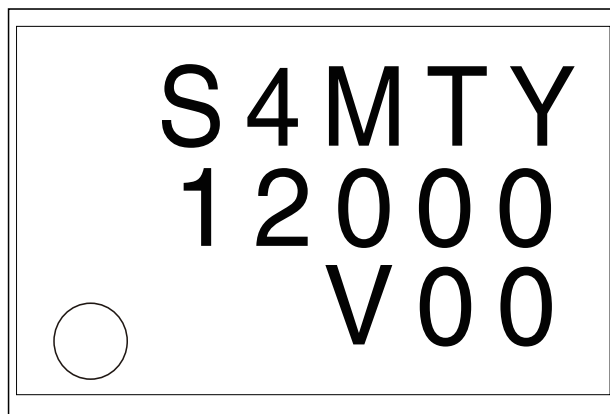
(2) MB85RS4MTYPN-G-AWEWE1

<div>8-pin plastic DFN</div> 	Lead pitch	1.27 mm
	Package width x Package length	5.00 mm × 6.00 mm
	Sealing method	Plastic mold
	Mounting height	0.90 mm MAX



■ MARKING (Example)

[MB85RS4MTYPF-G-BCE1]
[MB85RS4MTYPF-G-BCERE1]



[8-pin plastic SOP 208mil]

S4MTY: Product name
12000: 1(CS code) + 2000(Year and Week code)
V00: Trace code

[MB85RS4MTYPN-G-AWEWE1]



[8-pin plastic DFN 5mm x 6mm]

MB85RS4MTY: Product name
1E1: 1(CS code) + E1(Lead free code)
2000R00: 2000(Year and Week code) + R00(Trace code)

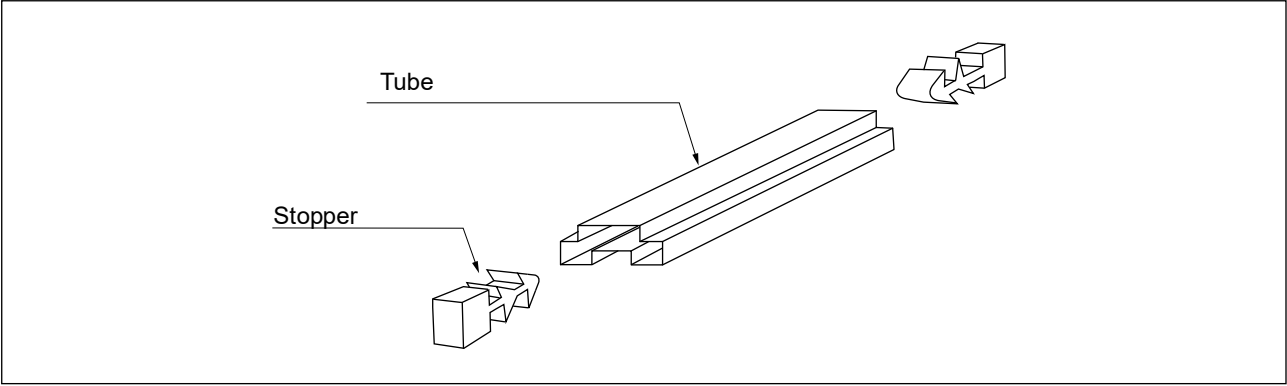
■ PACKING INFORMATION

(1) MB85RS4MTYPF-G-BCE1

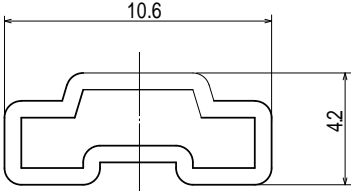
1. Tube

1.1 Tube Dimensions

- Tube/stopper shape (example)



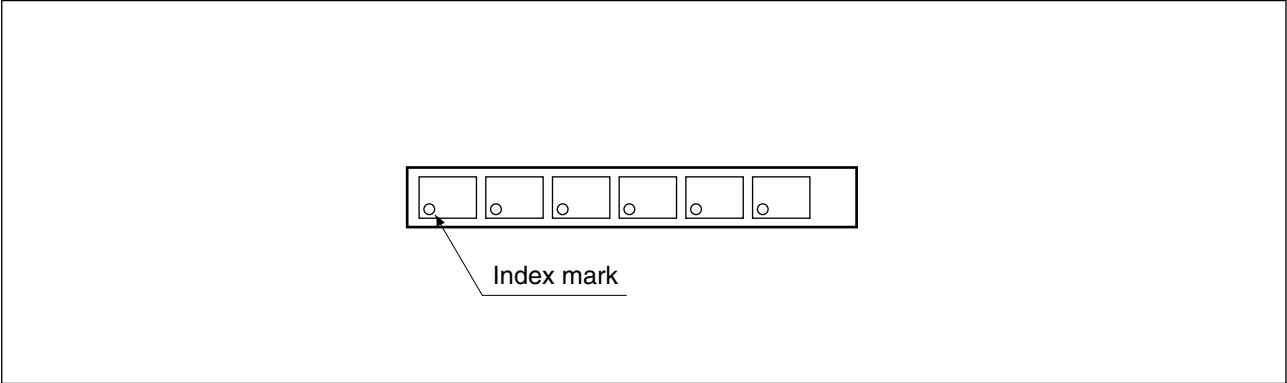
• Tube cross-sections and Maximum quantity

 <p>10.6</p> <p>42</p> <p>No heat resistance. Package should not be baked by using tube.</p>	Maximum quantity		
	pcs/tube	pcs/inner box	pcs/outer box
	80	4,000 (50 tube/inner box)	16,000 (Max:4 inner box/ outer box)

tube length:508

(Dimensions in mm)

• Direction of index in tube



MB85RS4MTY

1.2 Product label indicators (example)

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping)
 [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]

XXXXXXXXXXXXX (Part number)

(3N)1 XXXXXXXXXXXXXXXX XXX
(Part number and quantity)

G

Pb

(LEAD FREE mark)

QC PASS

(3N)2 XXXXXXXXXXXXXXXX XXXXXXXX
(Control number bar code)

XXX pcs (Quantity)

XXXXXXXXXXXXXXXXX (Part number)

XXXXXXXXXXXXXXXXX (Part number bar code)

XXXX/XX/XX (Packed years/month/day) ASSEMBLED IN xxxx

XXXXXXXXXXXXX (Part number)
(Control number bar code)

XX/XX
(Package count)

XXXX-XXX XXX
XXXX-XXX XXX

XXXXXXXXXXXXX (Control number) (Lot Number and quantity)

XXXXXXXXXXXXXXXXX (Comment)

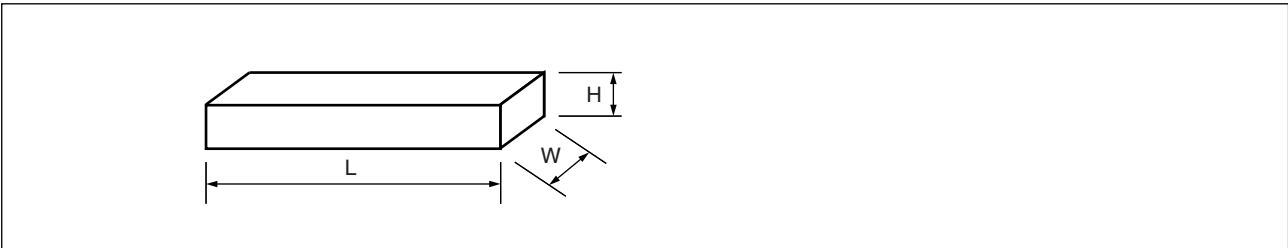
← C-3 Label

← Perforated line

← Supplemental Label

1.3 Dimensions for Containers

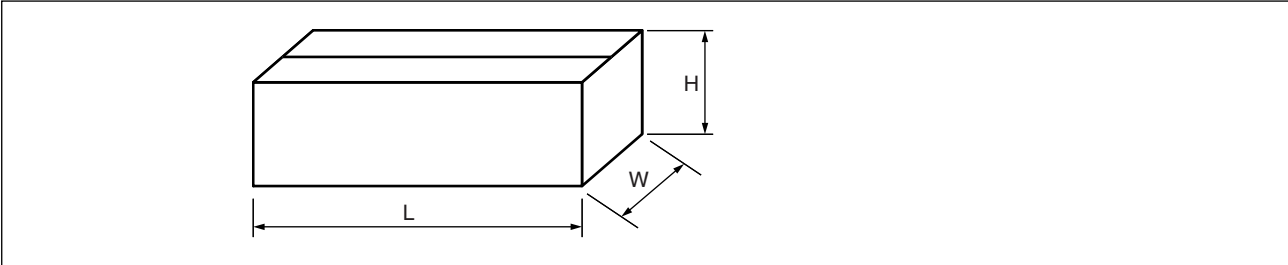
(1) Dimensions for inner box



L	W	H
540	125	75

(Dimensions in mm)

(2) Dimensions for outer box



L	W	H
565	270	180

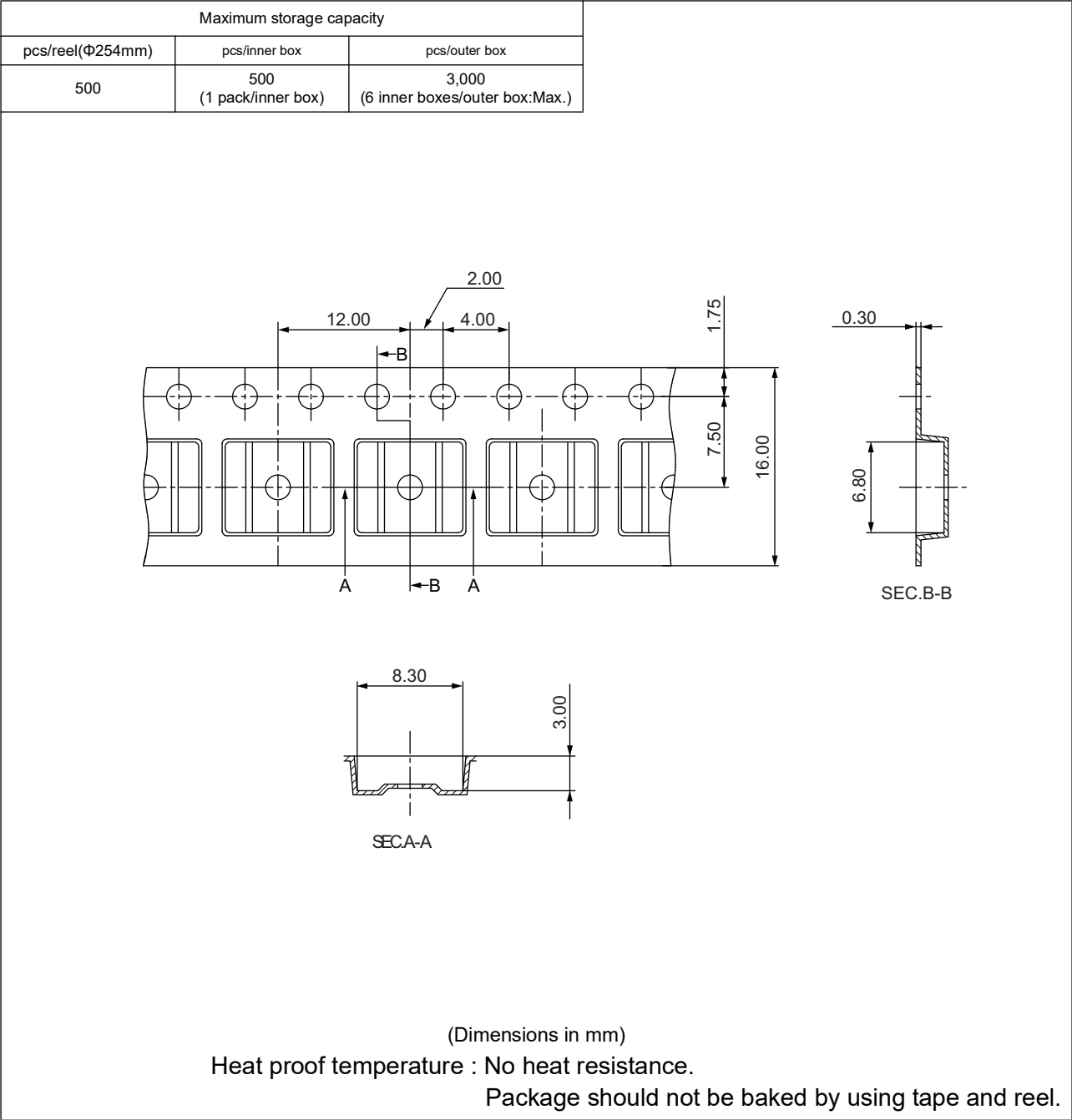
(Dimensions in mm)

(2) MB85RS4MTYPF-G-BCERE1/MB85RS4MTYPN-G-AWEWE1

1. Emboss Tape

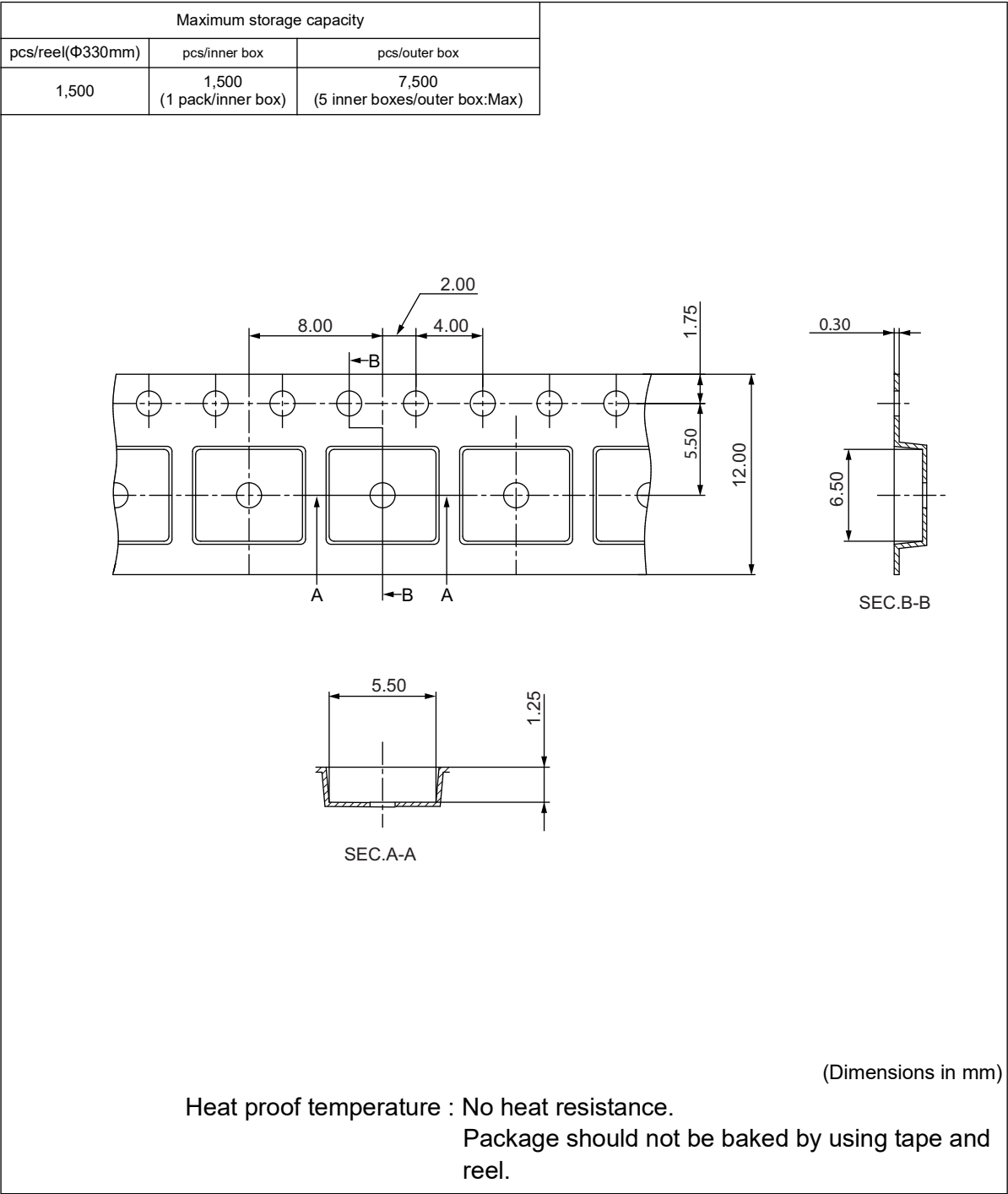
1.1 Tape Dimensions (not drawn to scale)

1.1.1 MB85RS4MTYPF-G-BCERE1 (8-pin plastic SOP 208mil)



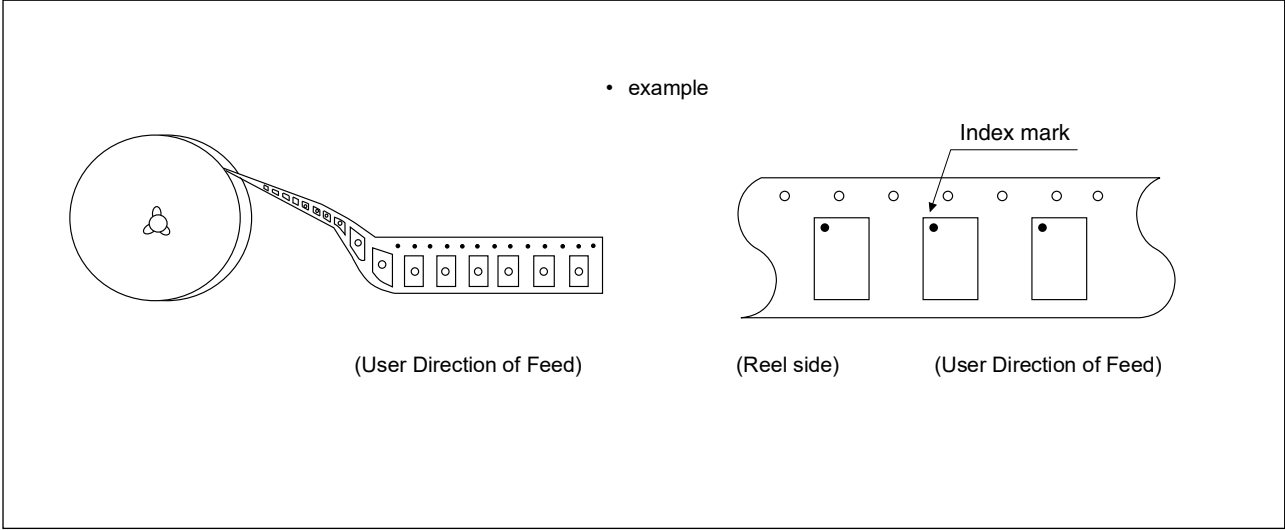
MB85RS4MTY

1.1.2MB85RS4MTYPN-G-AWEWE1 (8-pin plastic DFN 5mm × 6mm)

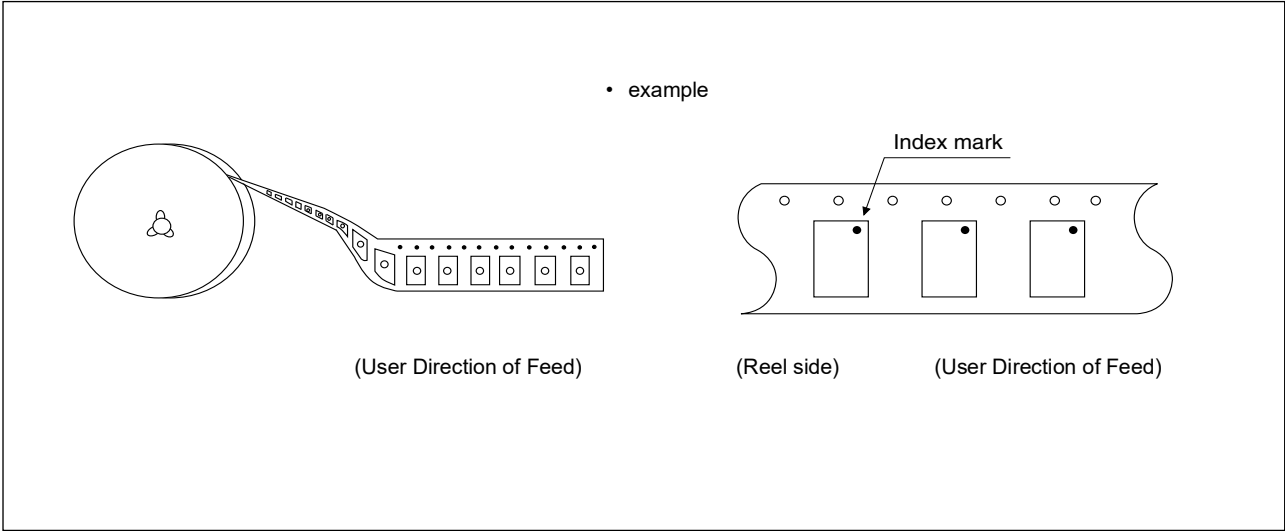


1.2 IC orientation

8-pin plastic SOP 208mil

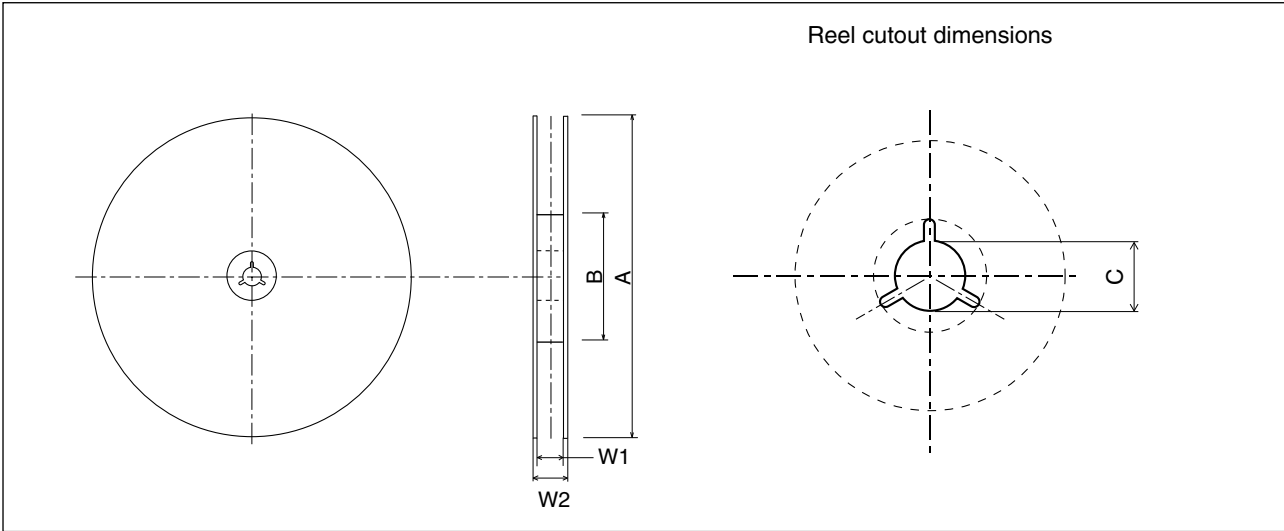


8-pin plastic DFN 5mm × 6mm



MB85RS4MTY

1.3 Reel dimensions

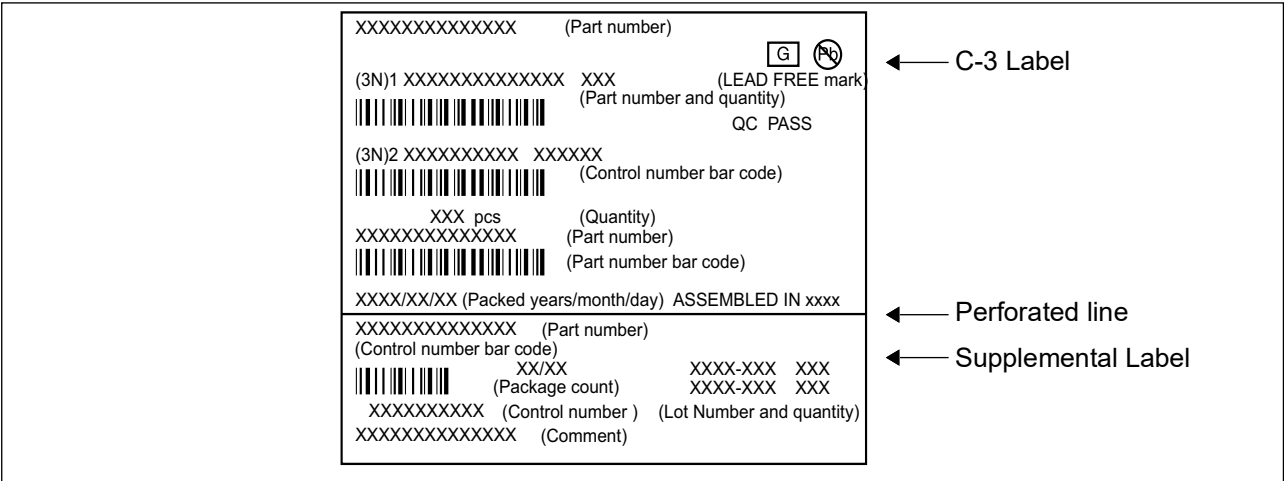


Dimensions in mm


	A	B	C	W1	W2
MB85RS4MTYPF-G-BCERE1	254	100	13	17.5	21.5
MB85RS4MTYPN-G-AWEWE1	330	100	13	13.5	17.5

1.4 Product label indicators (example)

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping)
[C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II: Moisture Barrier Bag (It sticks it on the Aluminum laminated bag)
SOP8 [MSL Label]



Caution
This bag contains
MOISTURE-SENSITIVE DEVICES

LEVEL

3

1. Calculated shelf life in sealed bag: 24 months at <40°C and <90% relative humidity (RH)
2. Peak package body temperature: 260°C
3. After bag is opened, devices that will be subjected to reflow solder or other high temperature process must be
 - a) Mounted within: 168 hours of factory conditions <30°C/60% RH, or
 - b) Stored per J-STD-033
4. Devices require bake, before mounting, if:
 - a) Humidity Indicator Card reads >10% for level 2a - 5a devices or >60% for level 2 devices when read at 23 ± 5°C
 - b) 3a or 3b are not met
5. If baking is required, refer to IPC/JEDEC J-STD-033 for bake procedure

Bag Seal Date: see adjacent bar code label.

Note: Level and body temperature defined by IPC/JEDEC J-STD-020

← MSL label

DFN8 [MSL Label]

MOISTURE-SENSITIVE DEVICES

注意

1. ドライバック包装の保管期限は、24 ヶ月（25°C/80%RH未満）です。
2. 本製品の耐熱温度は、260°C です。
3. 袋開封後は、下記a) b)条件下で、ご使用ください。
 - a) 168 時間以内 (30°C/60%RH以下)
 - b) J-STD-033条件
4. 以下の条件の場合は、実装前にベークしてください。
 - a) 23±5°Cの環境下でインジケータカードの10%を超えた場合
 - b) 3a、3bの条件に合致しない場合
5. ベーク必要な場合はIPC/JEDEC J-STD-033 参照してください。

CAUTION

1. Calculated shelf life in sealed bag: 24 months at <25°C / 80% RH
2. Peak package body temperature: 260°C
3. After bag is opened, devices that will be subjected to reflow solder or other high temperature process must
 - a) Mounted within: 168 hours of factory conditions ≤30°C/60%RH
 - b) Stored per J-STD-033
4. Devices require bake, before mounting, if:
 - a) Humidity Indicator Card is > 10% when read at 23±5°C
 - b) 3a or 3b not met.
5. If baking is required, refer to IPC/JEDEC J-STD-033 for bake procedure.

LEVEL

3



包装日：品名ラベルをご確認下さい
Bag Seal Date: See adjacent bar code label



* F 0 0 0 1 *

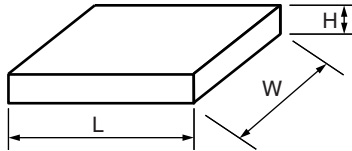
Note: Level and body temperature defined by IPC/JEDEC J-STD-020

← MSL label

MB85RS4MTY

1.5 Dimensions for Containers

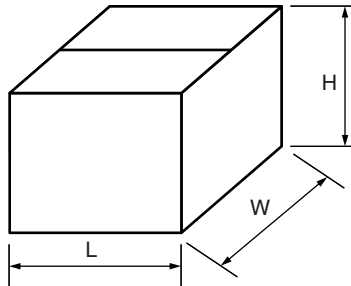
(1) Dimensions for inner box



	L	W	H
MB85RS4MTYPF-G-BCERE1	265	260	50
MB85RS4MTYPN-G-AWEWE1	350	335	35

(Dimensions in mm)

(2) Dimensions for outer box



	L	W	H
MB85RS4MTYPF-G-BCERE1	565	270	180
MB85RS4MTYPN-G-AWEWE1	384	368	225

(Dimensions in mm)

■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn left side of that page.

Page	Section	Change Results
1,23	High endurance	10^{13} times/byte → 10^{13} times(+125 °C), 10^{14} times(+85 °C)
1,22	Data Retention	50.4 years(+ 85 °C)→ 70.4 years(+ 85 °C), 13.7 years(+ 105 °C)→ 19.1 years(+ 105 °C), 4.2 years(+ 125 °C)→ 5.9 years(+ 125 °C)
23	Read/Write endurance about FeRAM	Add information

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